

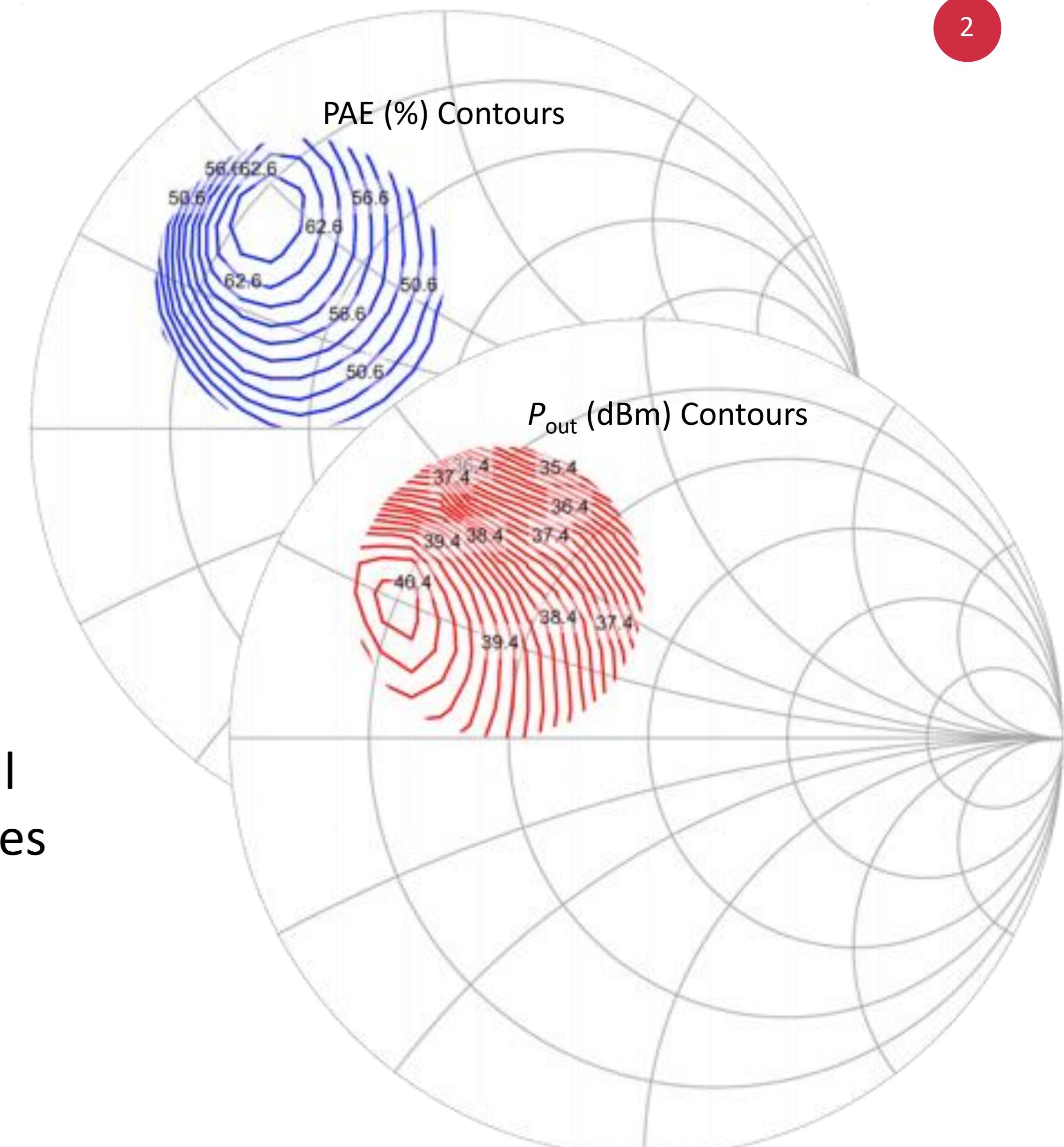
Load-pull techniques for 5G and 6G applications – state of the art and future

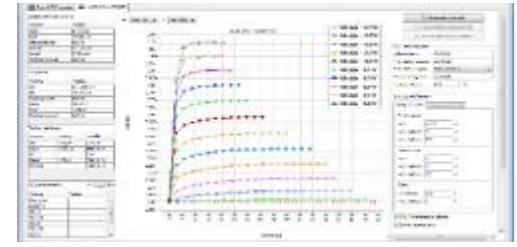
Mauro Marchetti



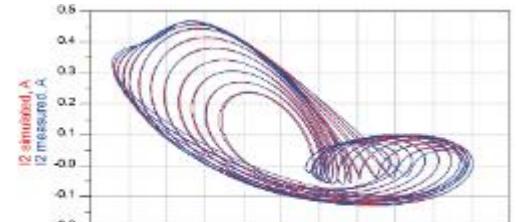
Motivation for Load pull

- S-parameters provide information about linear response of the device under test (DUT)
- Transistor performance is highly dependent on its load impedance
- RF/Microwave transistors exhibit non-linear behavior:
 - harmonic generation
 - frequency mixing, etc.
- Load-pull enables characterisation of the linear and non-linear DUT behaviour under large-signal excitations and non- $50\ \Omega$ source/load impedances

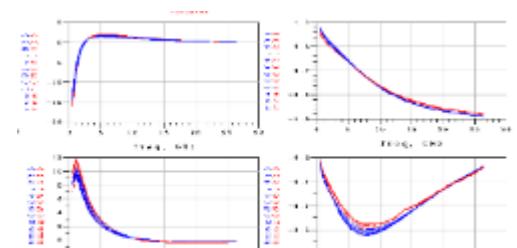




Transistor characterization



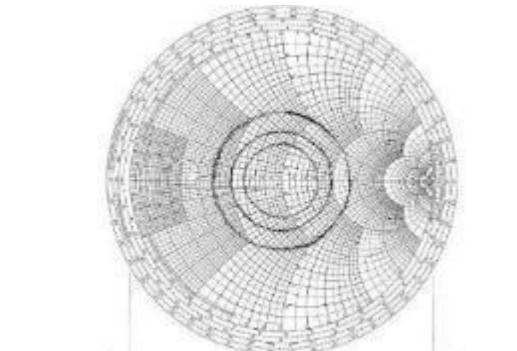
Compact transistor model validation



Behavioral model extraction



Matching network design (PA, LNA...)

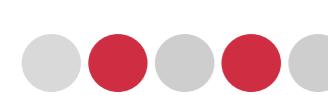


Performance test / reliability test



Bandwidth Requirements by Application

Application	Frequency Range	Single Channel Bandwidth	Total Bandwidth (1 Channel + ACLR)	Optimum Channels For Test	Total Bandwidth (n Channels + ACLR)
W-CDMA	800 MHz – 3.5 GHz	5 MHz	15 MHz	5	25 MHz
Multi-carrier W-CDMA	800 MHz – 3.5 GHz	15 MHz	25 MHz	7	35 MHz
LTE	600 MHz – 6 GHz	20 MHz	60 MHz	5	100 MHz
802.11a/b/g	2.4 GHz	20 MHz	60 MHz	5	100 MHz
802.11n	2.4 GHz, 5 GHz	40 MHz	160 MHz	5	200 MHz
LTE-A	800 MHz – 3.5 GHz	100 MHz	300 MHz	5	500 MHz
802.11ac	5 GHz	160 MHz	480 MHz	3	480 MHz
802.11ax	2.4 / 5 GHz	160 MHz	480 MHz	3	480 MHz
5G	600 MHz – 6 GHz	100 MHz	300 MHz	4	600 MHz
5G	28 GHz	400 MHz			
5G	38 GHz	~1 GHz			
6G	95 GHz – 3 THz ???				



5G (and 6G) Challenges for load pull

Higher frequencies → higher losses

Higher bandwidth → modulated signals characterization,
phase skew

Higher PAR → higher dynamic range

Higher level of integration → new test requirements

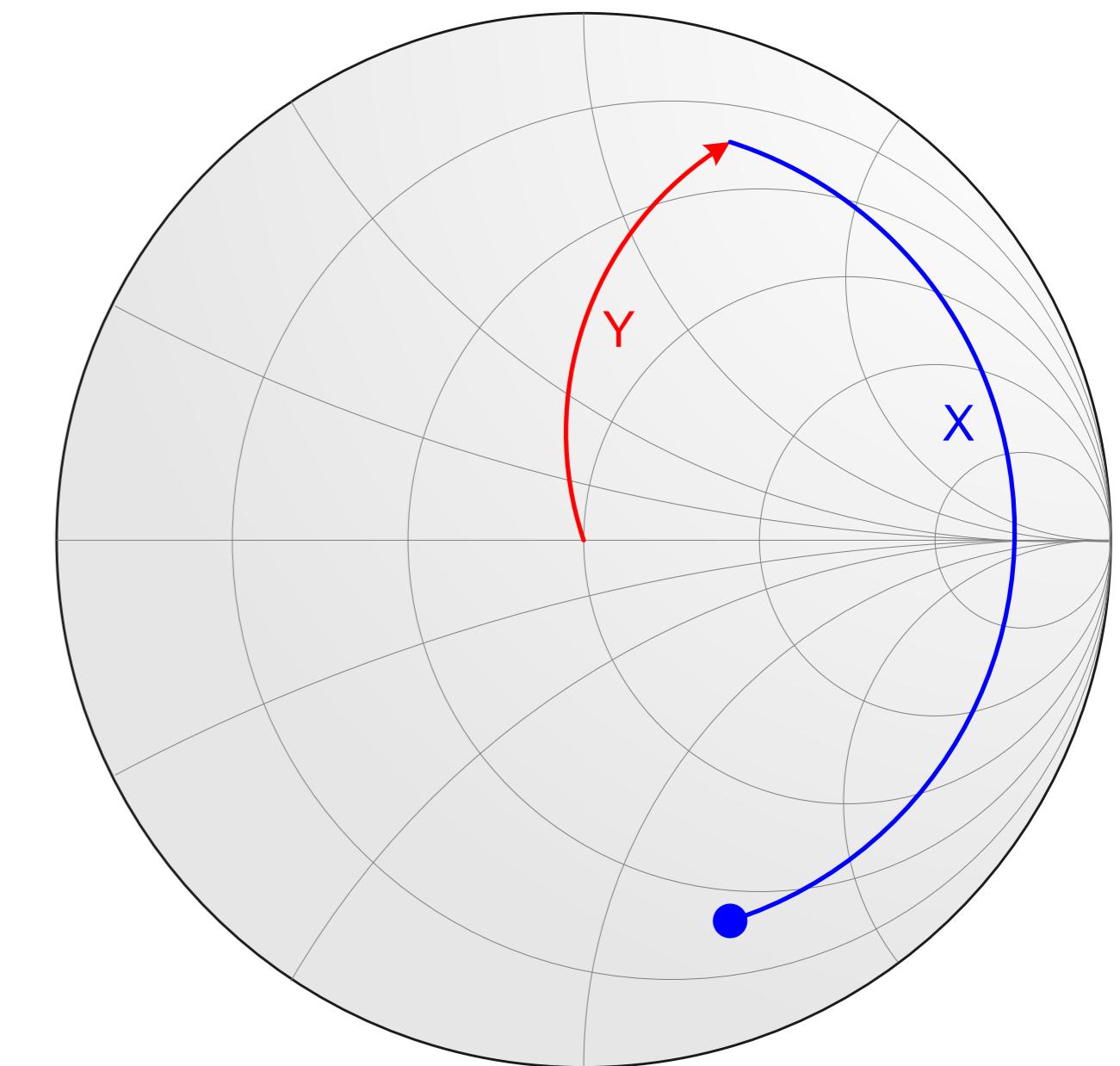
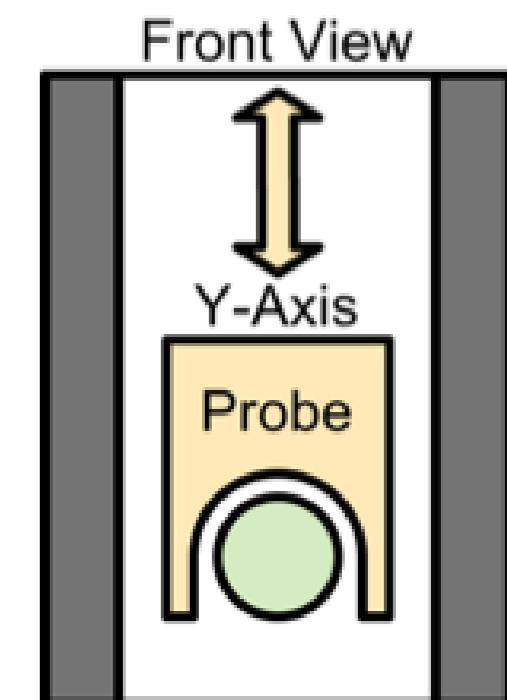
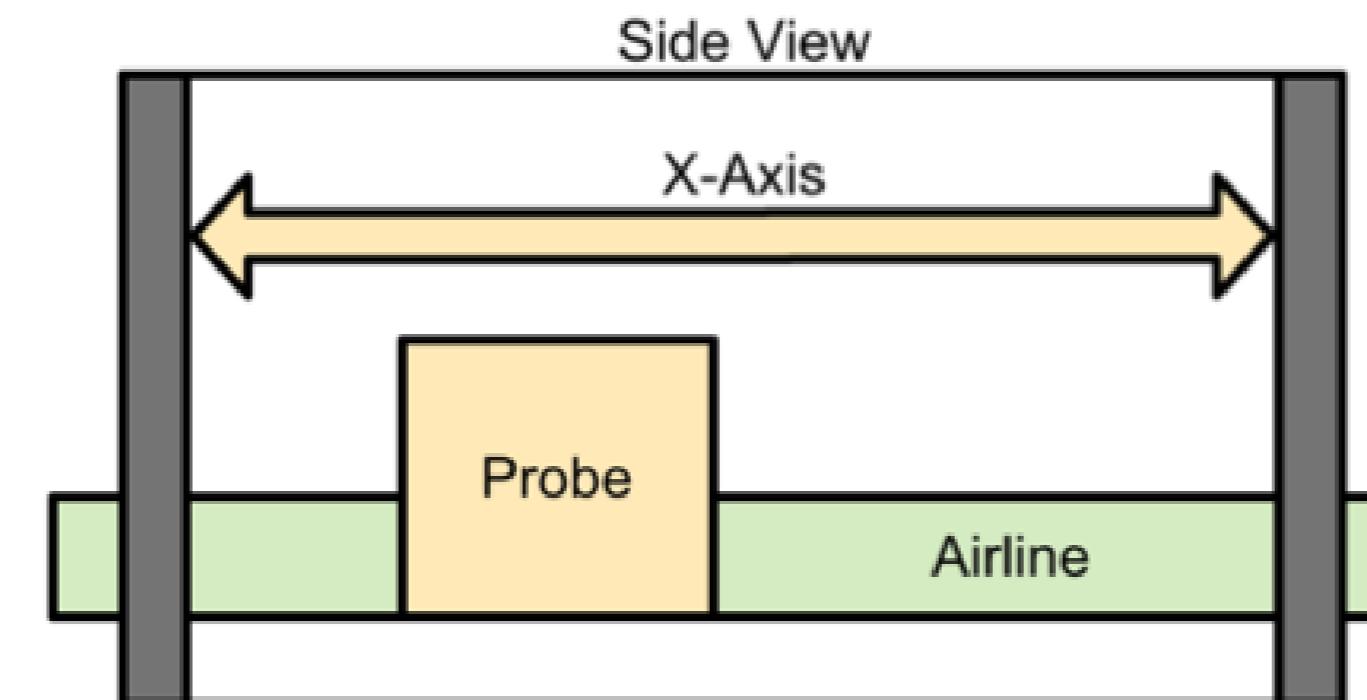
Passive tuning



●●●●● Slide-screw impedance tuners

- Probe movement above airline controls the reflection coefficient (Γ)
- Movement on X-axis controls phase of Γ
- Movement on Y-axis controls magnitude of Γ
- $|\Gamma|$ is always less than 1 as tuner introduces dissipative loss
- Loss increases with frequency thus Γ tunable range shrinks

$$\Gamma_{Load,n}(f_n) = \frac{a_{2,n}(f_n)}{b_{2,n}(f_n)}$$





Important considerations

- **Speed:**
 - DVT applications require hundreds of measurements to cover different signal bands and modulation types. Tuning speed is essential
- **Accuracy:**
 - Check and balance to gain confidence in your data
- **On wafer measurements:**
 - Adding components in front of the tuner element will:
 - Reduce the tuning range at the DUT reference
 - Increase the phase skew of the selected impedance against the signal BW

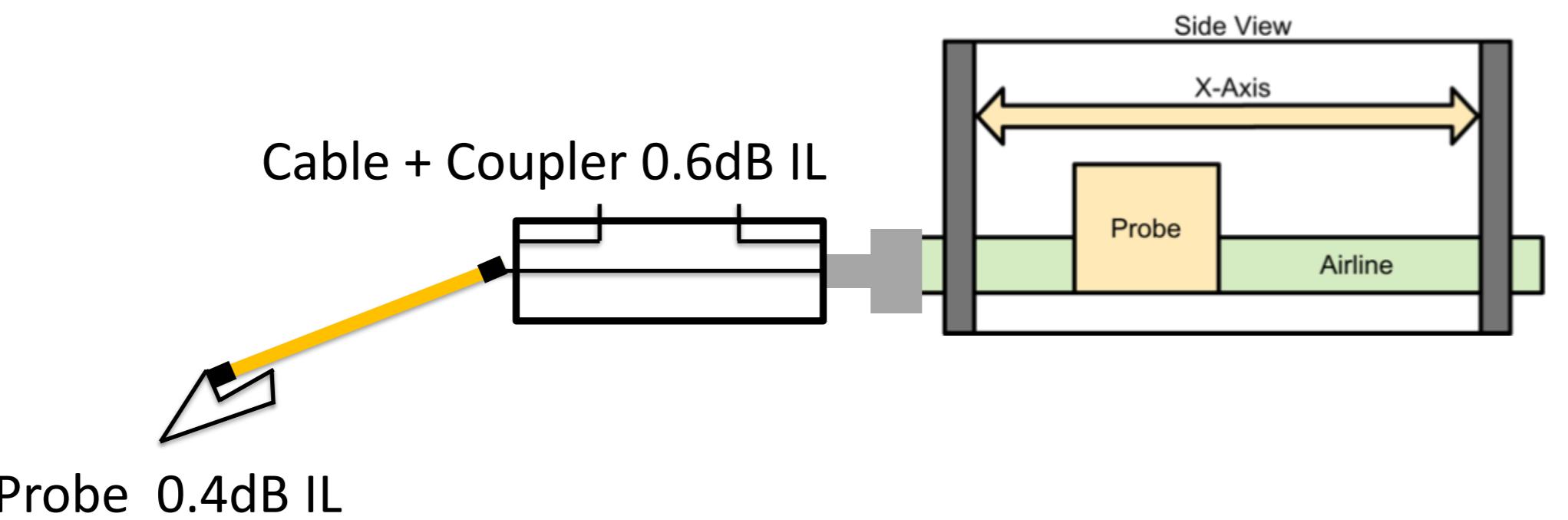


Tuning range

Frequency

28 GHz

- $VSWR_{tuner} = 15:1 \rightarrow |\Gamma_{tuner}| = 0.87$
- $IL_{coupler + cable + probe} = 1 dB$
- $VSWR_{Load} = 5.6:1 \rightarrow |\Gamma_{load}| = 0.69$



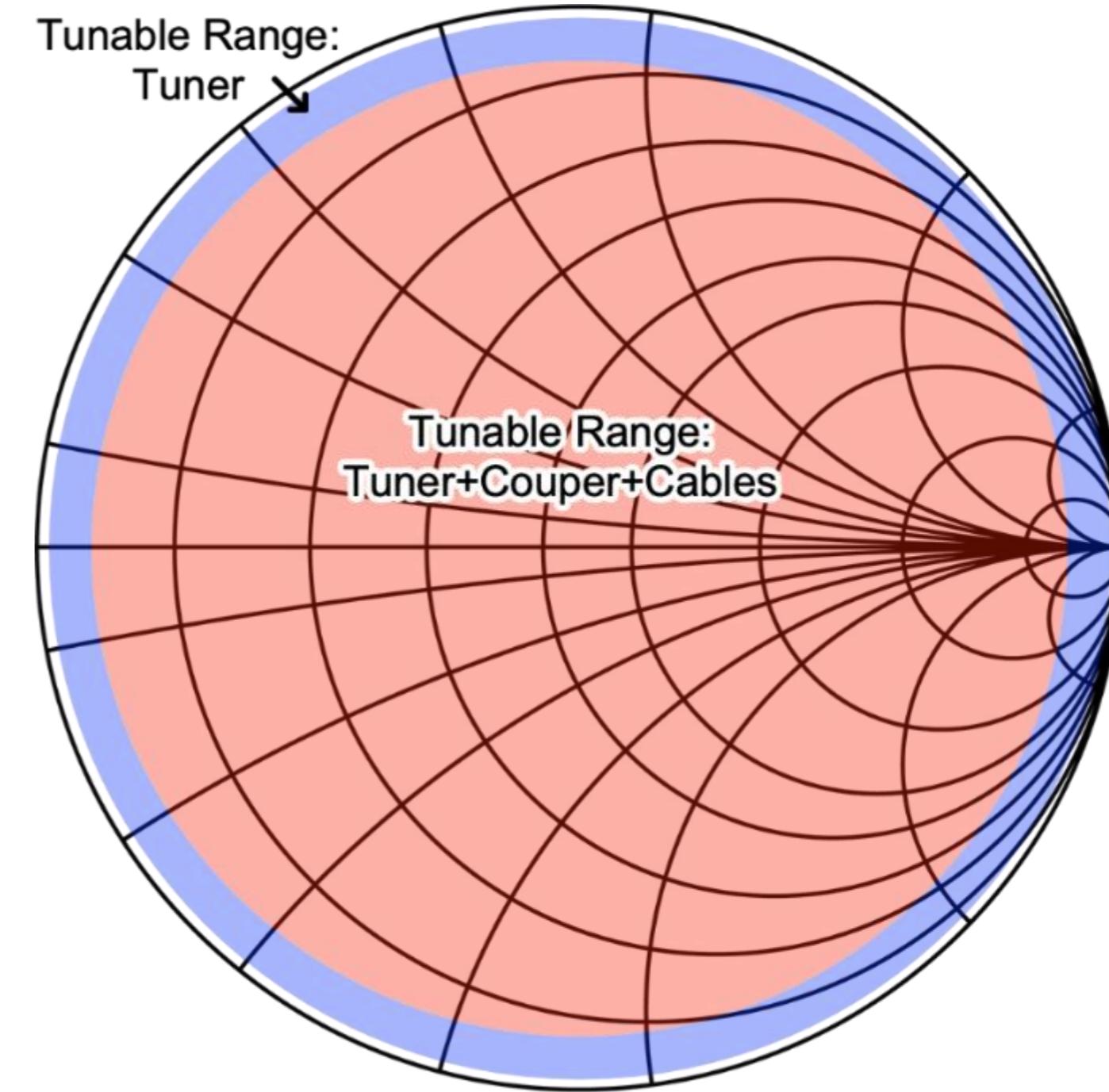
Ref. formulas:

$$RL_{tuner} + RL_{coupler+cable+probe} = RL_{dut}$$

$$RL_{tuner} = -20 \log\left(\frac{VSWR_{tuner} - 1}{VSWR_{tuner} + 1}\right)$$

$$RL_{coupler+cable+probe} = 2(IL_{coupler+cable+probe})$$

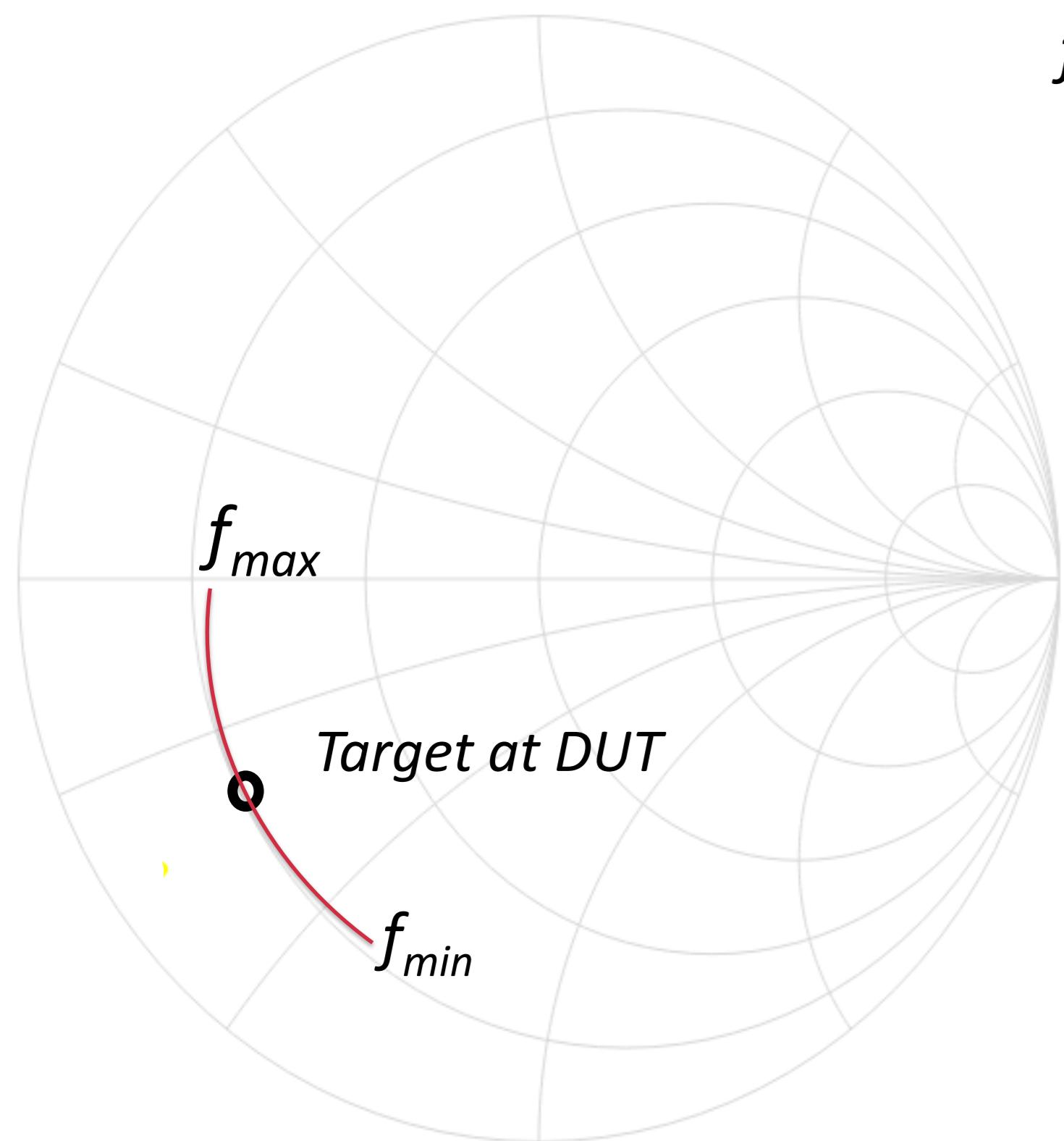
$$\Gamma_{dut} = 10^{\left(\frac{-RL_{dut}}{20}\right)}$$



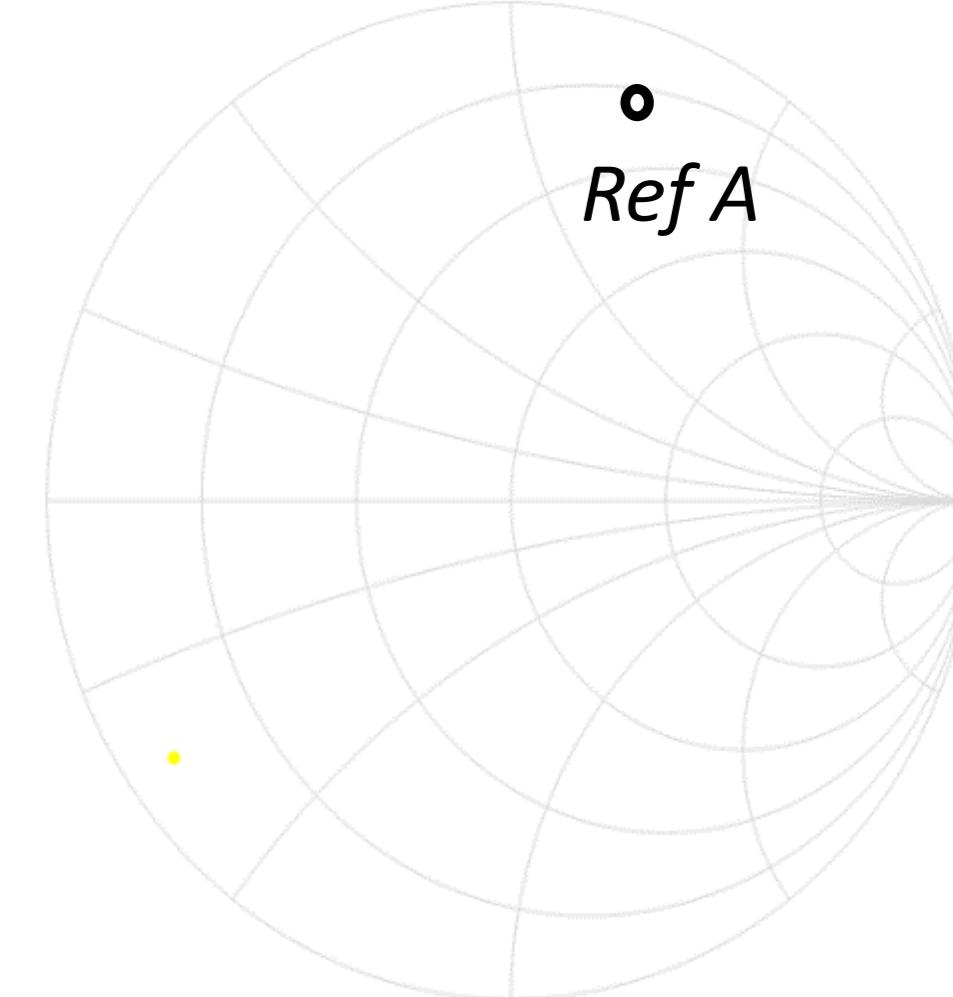
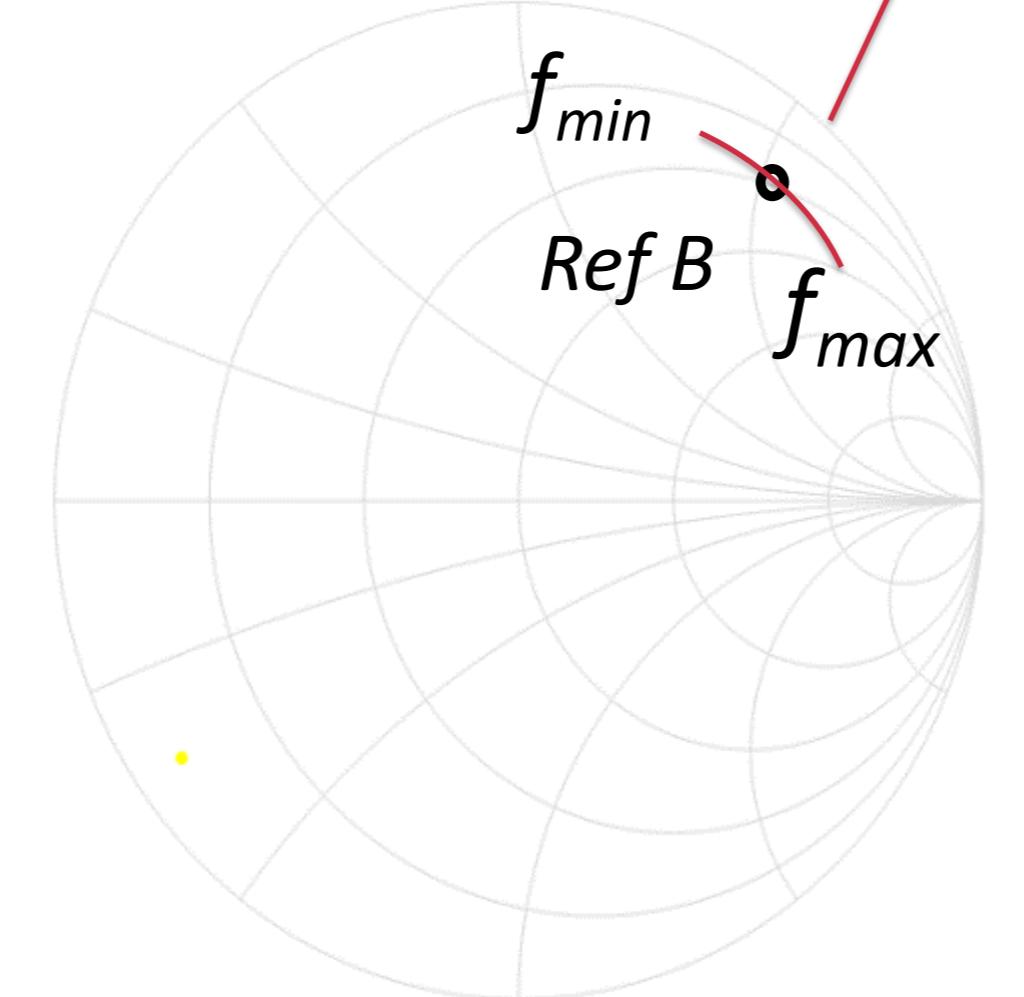
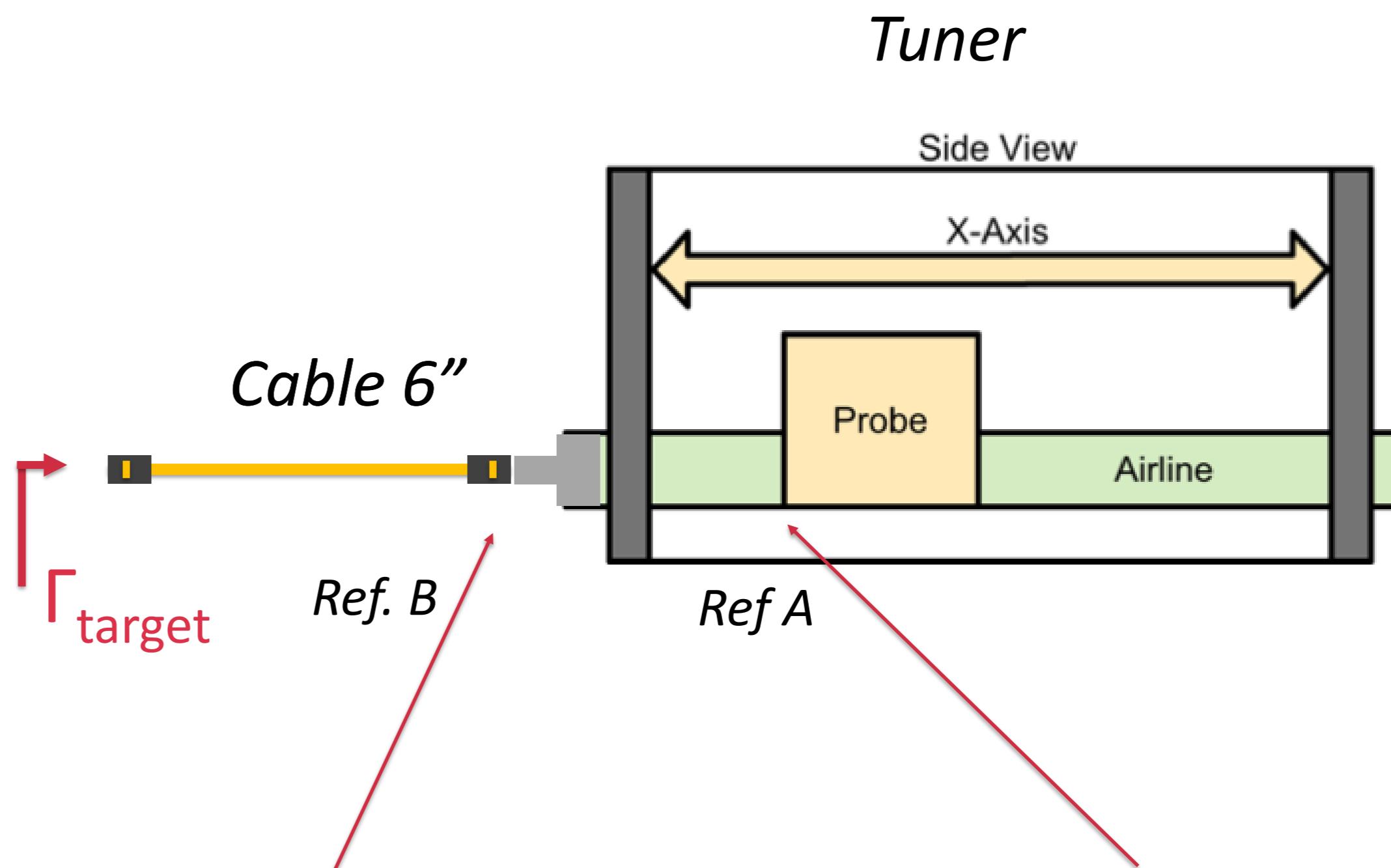
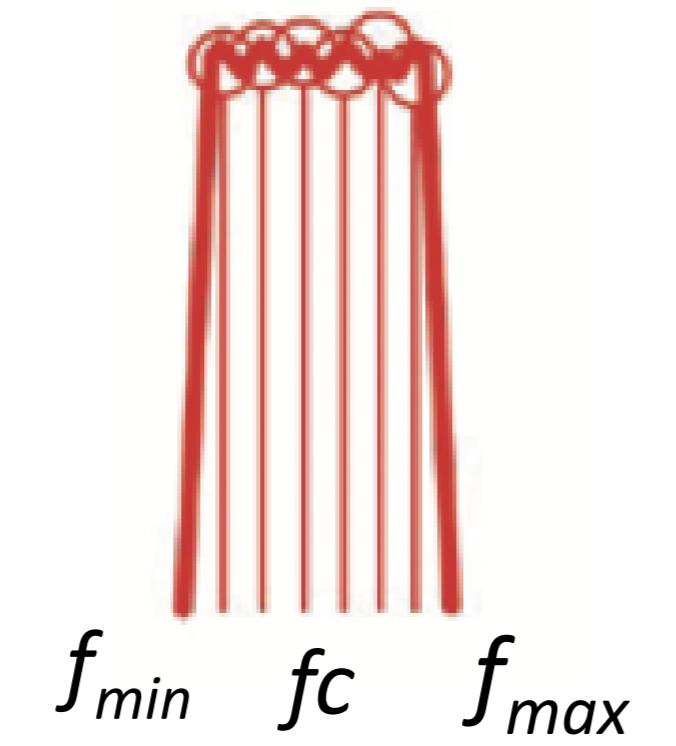


Phase skew

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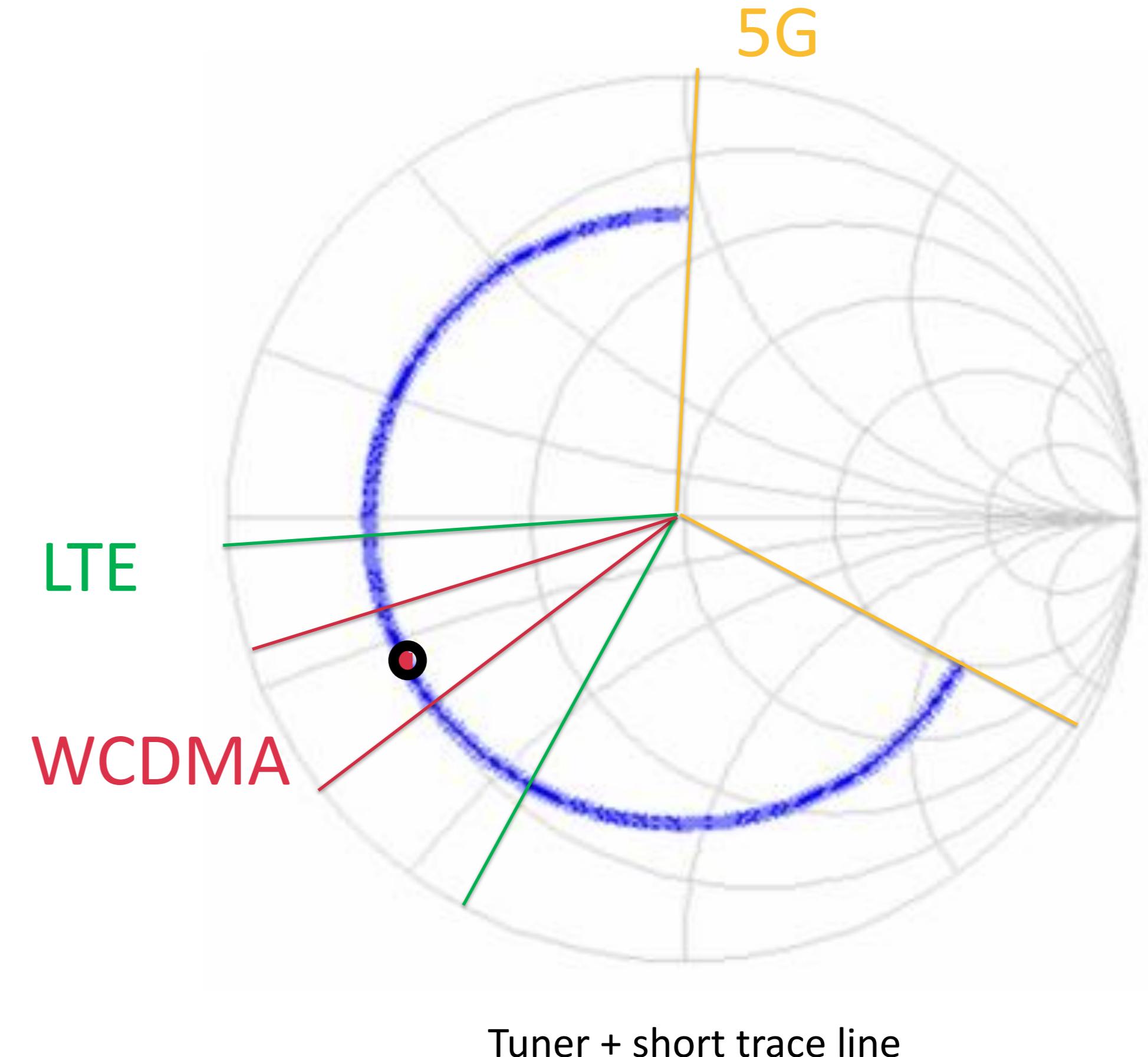
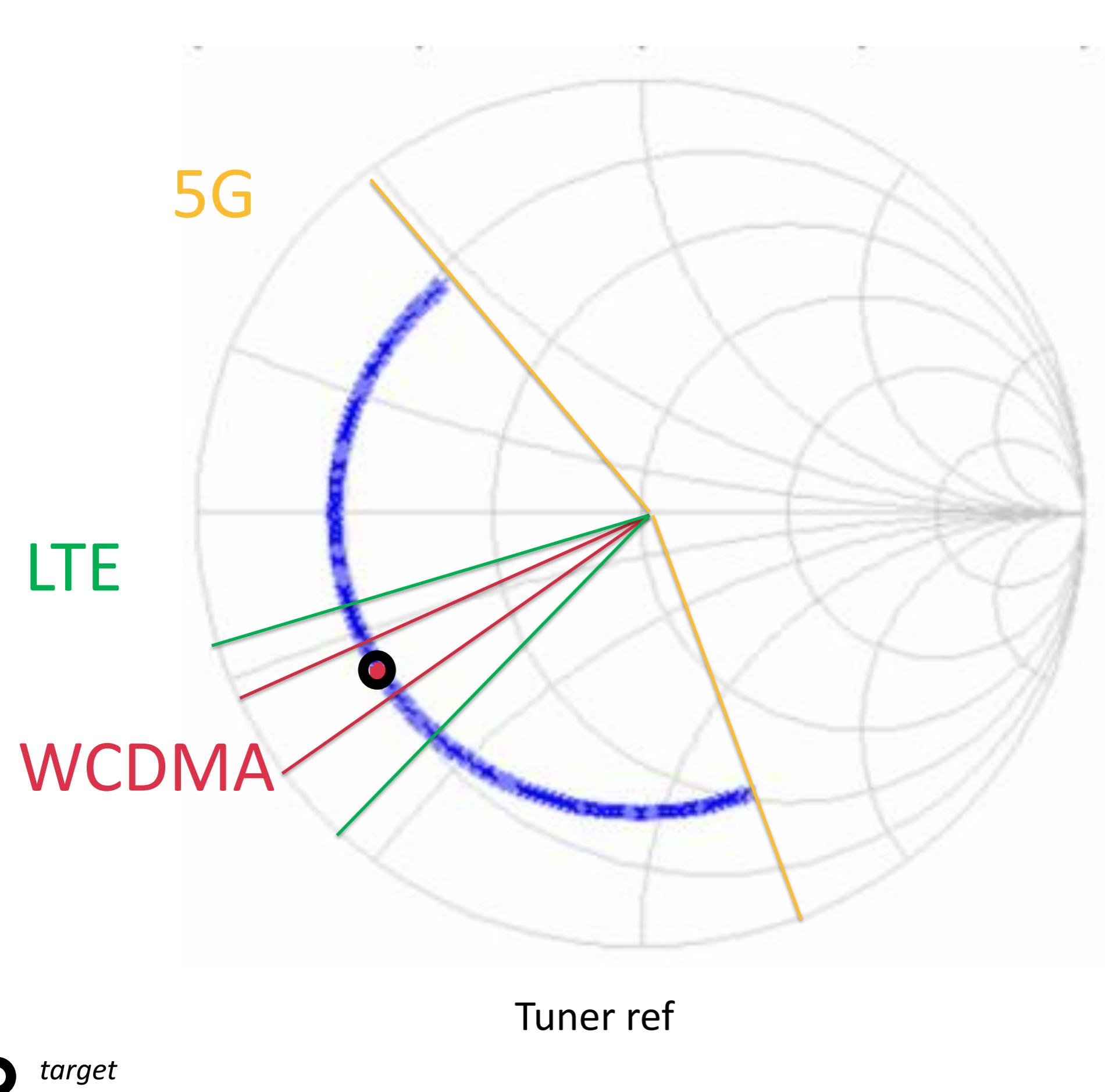


Modulated signal





Phase skew



●●●● FR2 and Nano5G

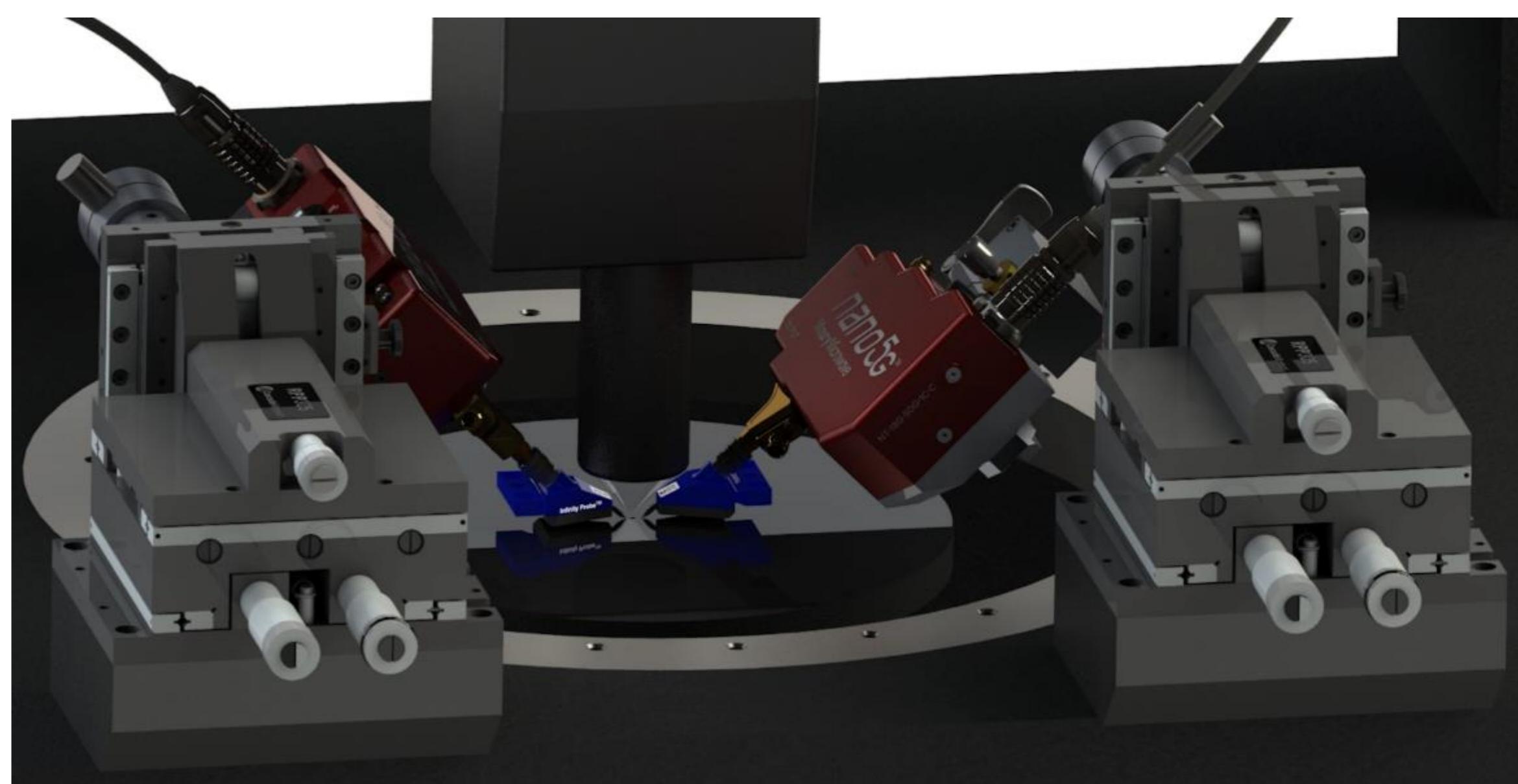
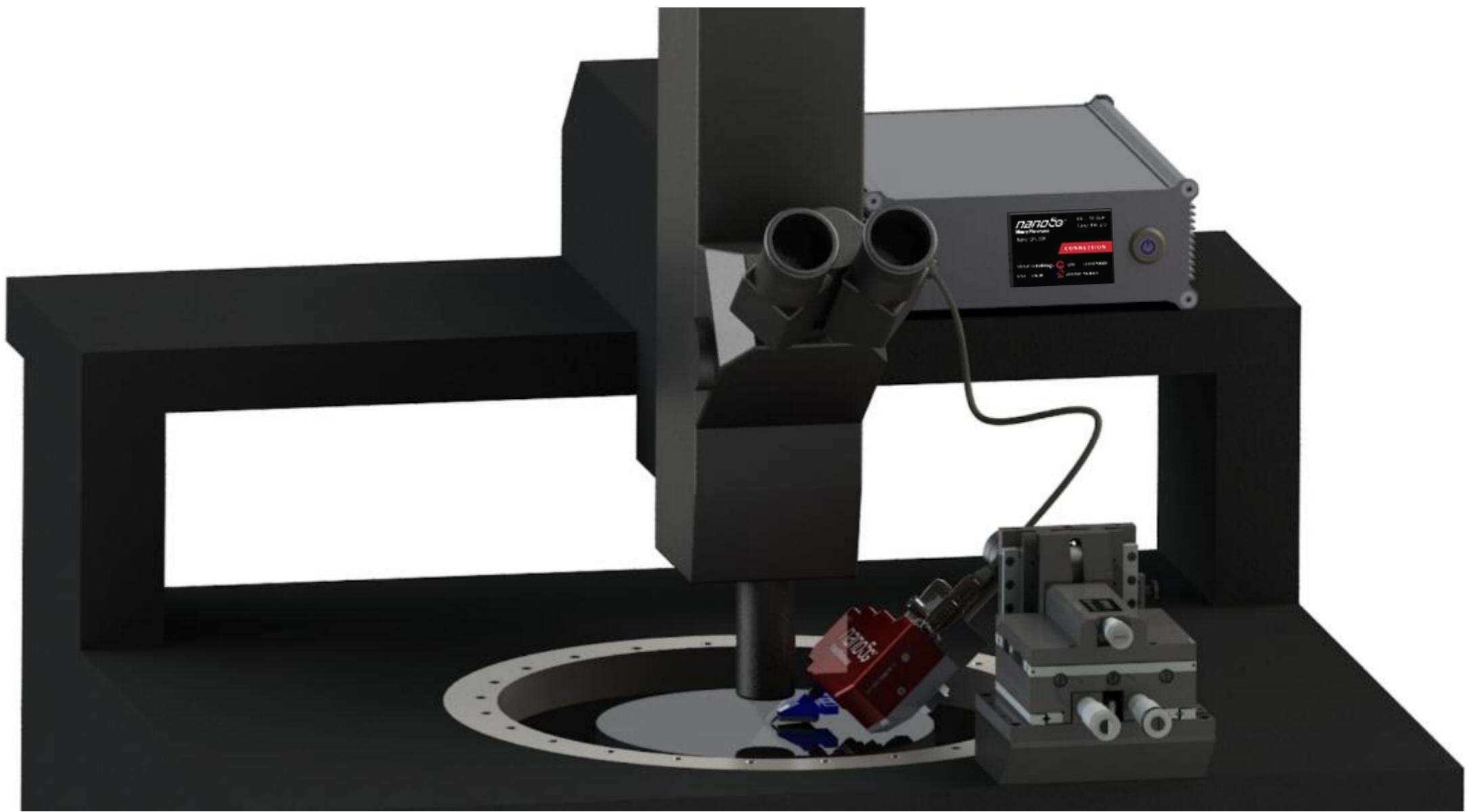
Challenges:

- Tuning range
- Phase skew
- Speed and accuracy
- Easy SW integration

Maury is introducing at IMS2021 **Nano5G**,
18 GHz-50 GHz tuner directly mounted to probe:

Nano5G:

- 1/10 of the volume and weight of other solutions:
 - Weight: 0.7 lbs
 - Dimensions: 2.35" x 1.57" x 4.5"
- No cable needed between probe and tuner
- Integrated coupler (optional)



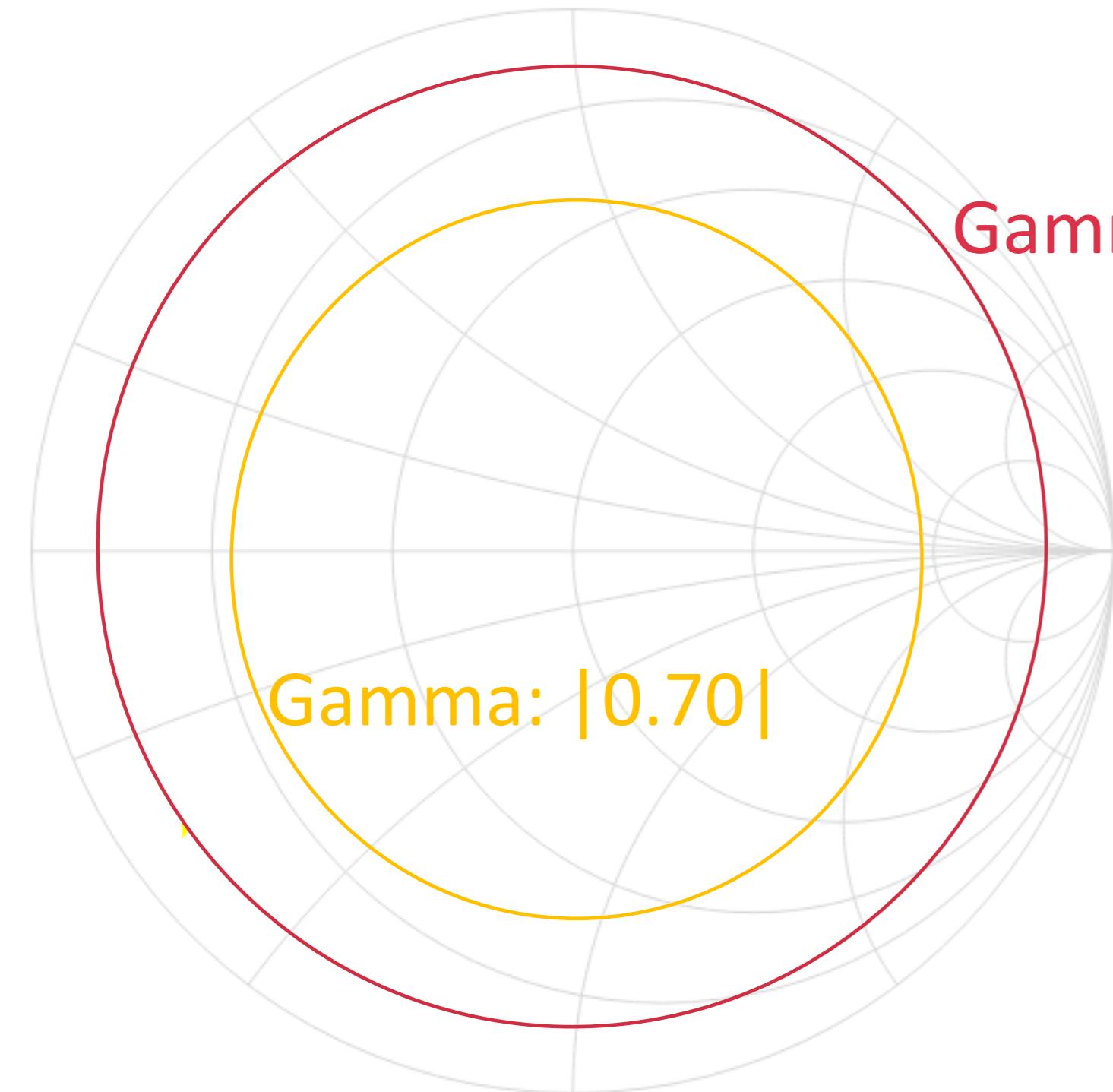


Features and benefits

Frequency

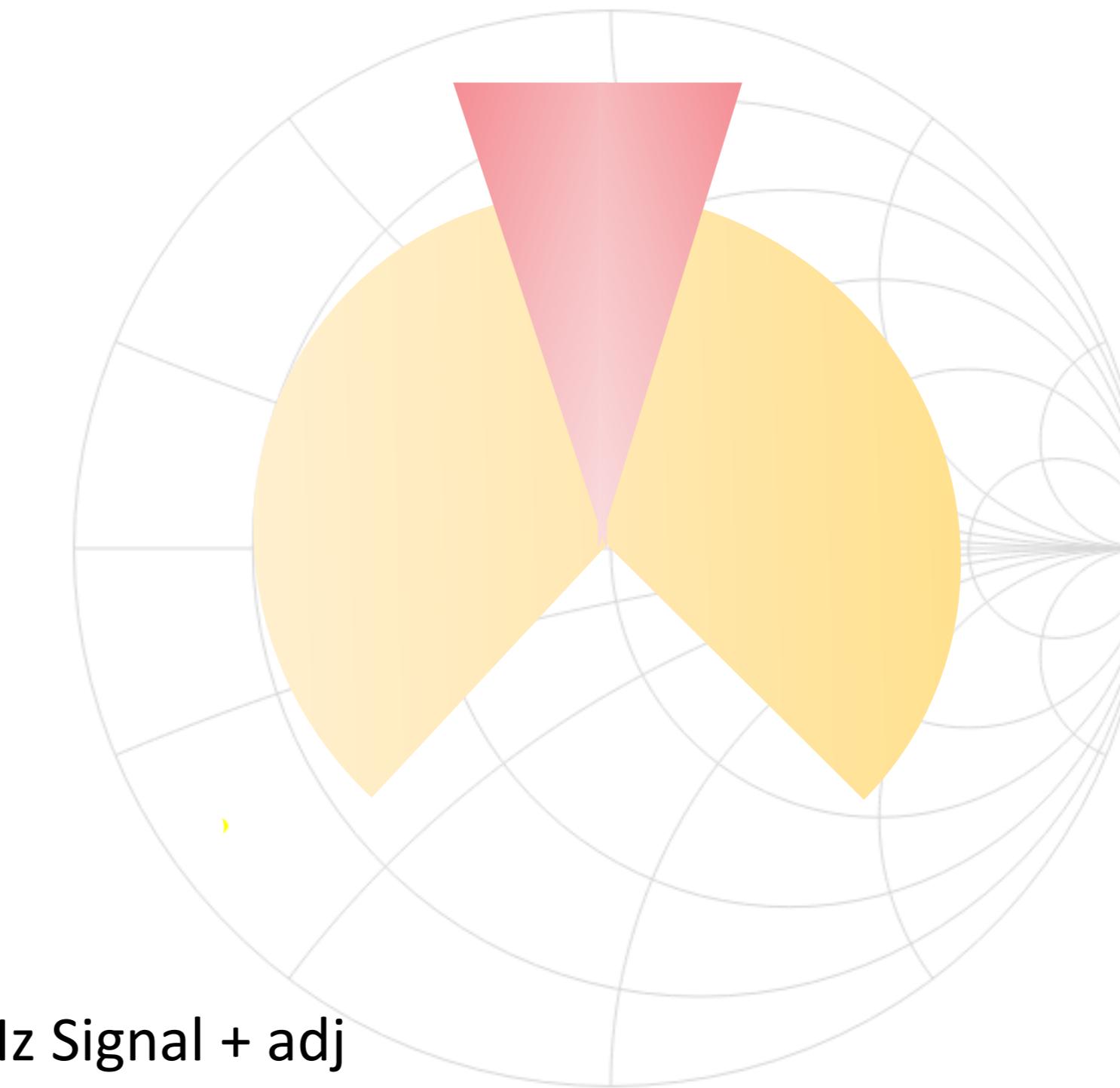
28 GHz

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Tuning range

(MT984AL01 + coupler with integration cable + probe vs Nano5G + probe)



100MHz Signal + adj
channels (left and right)

Phase skew

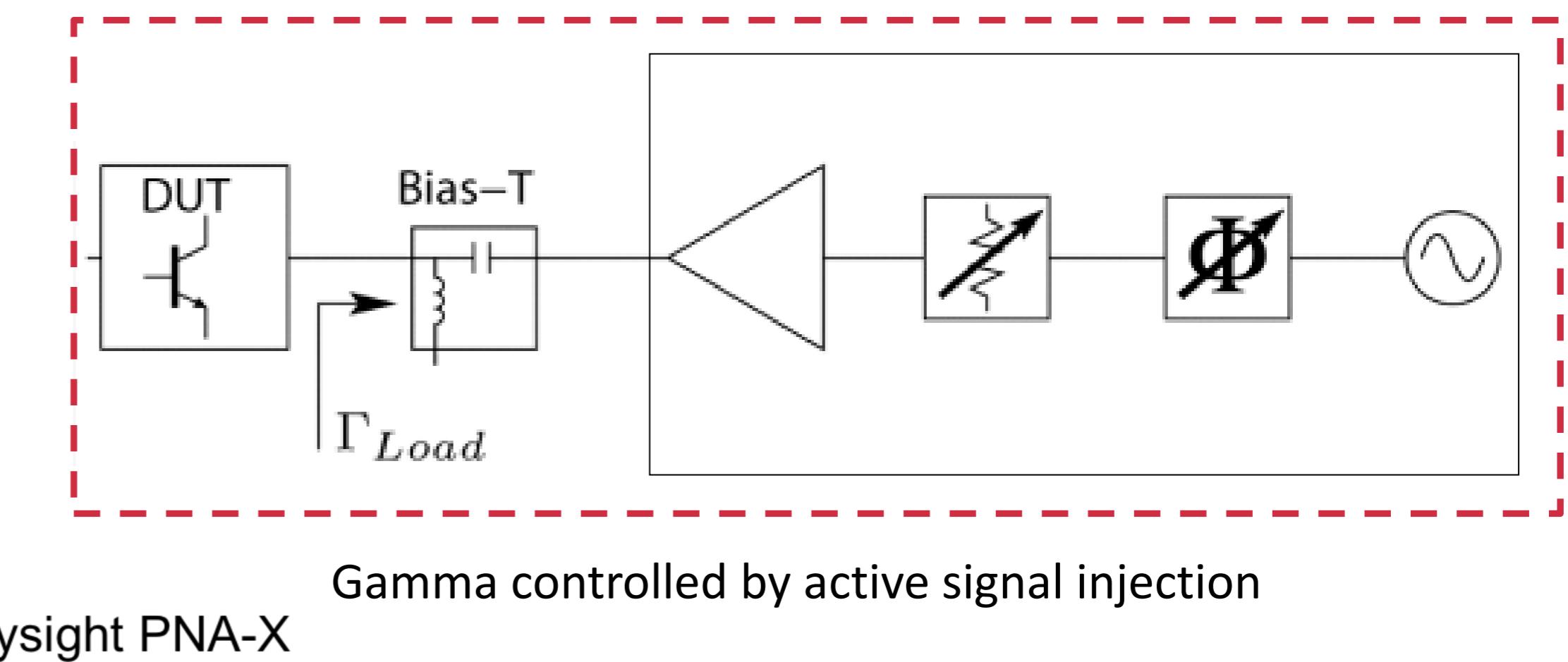
(MT984AL01 + coupler with integration cable + probe vs Nano5G + probe)

Active tuning

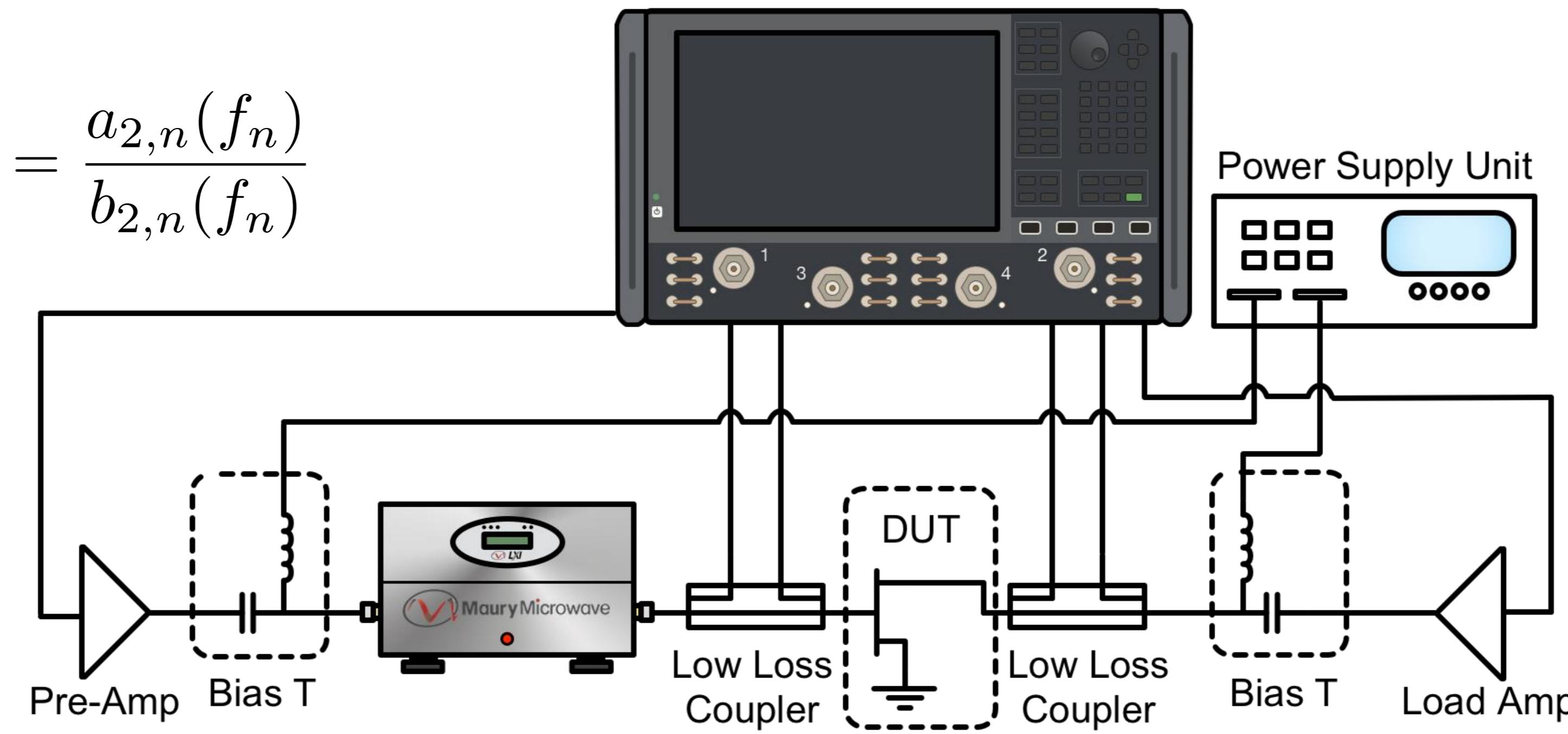


Active load pull

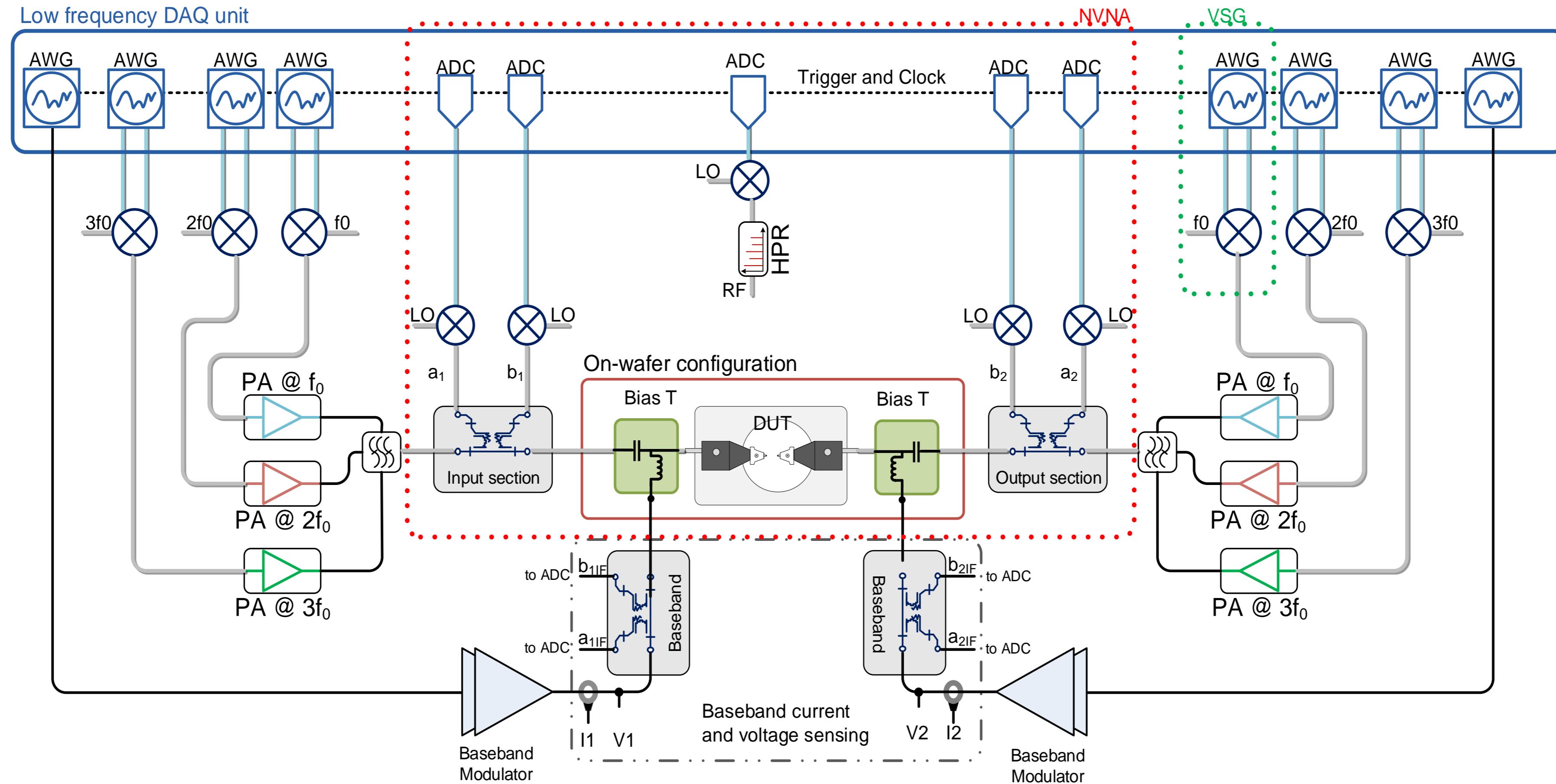
- Active signal injection used for impedance control
- Measures vector incident and reflected (a_x and b_x) waves
- Measurements performed at calibrated DUT reference plane
- Enables $|\Gamma|_{\text{Load}} = 1$ and even $|\Gamma|_{\text{Load}} > 1$



$$\Gamma_{\text{Load},n}(f_n) = \frac{a_{2,n}(f_n)}{b_{2,n}(f_n)}$$



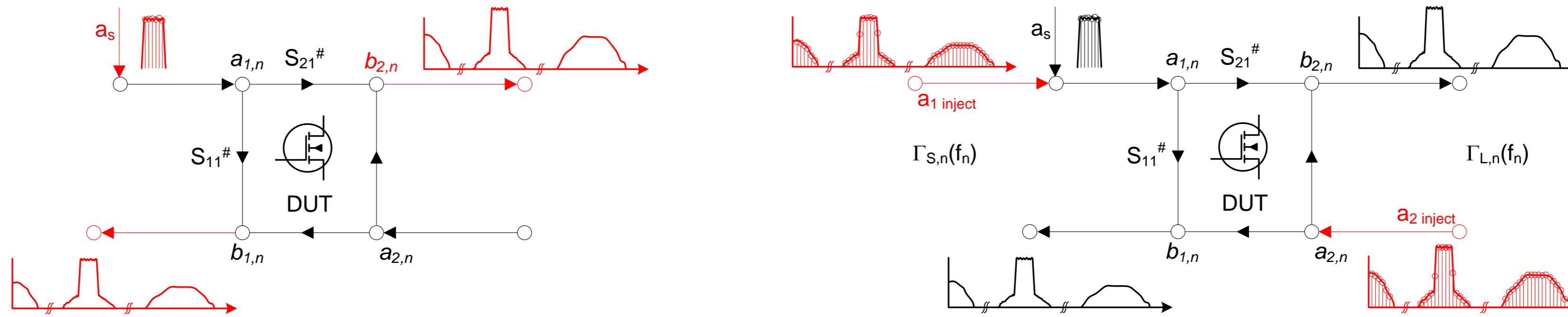
MT2000 mixed-signal vector load-pull for modulated signal characterization



- (N)VNA-like receiver architecture without narrowband filtering in order to allow wideband modulation acquisition
- Multiple vector signal generators (AWGs) are used as active tuners



Wideband Load Pull Algorithm

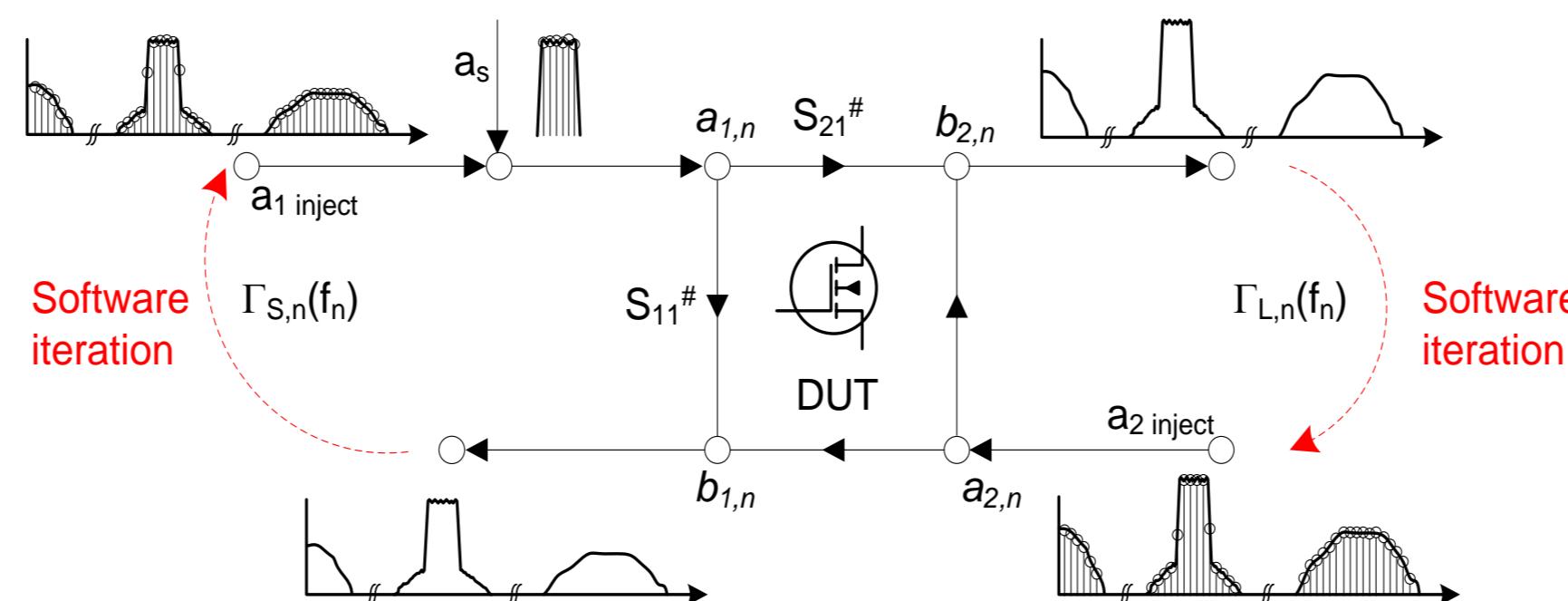


Step 1: A non-linear device excited with a modulated signal will emanate waves (b-waves) at the harmonic and baseband frequencies

Step 2: By measuring the Γ at the DUT, the a-waves to be injected to obtain a user-specified reflection coefficient can be estimated.

$$\Gamma_{x,n}(f_n) = \frac{a_{x,n}(f_n)}{b_{x,n}(f_n)}$$

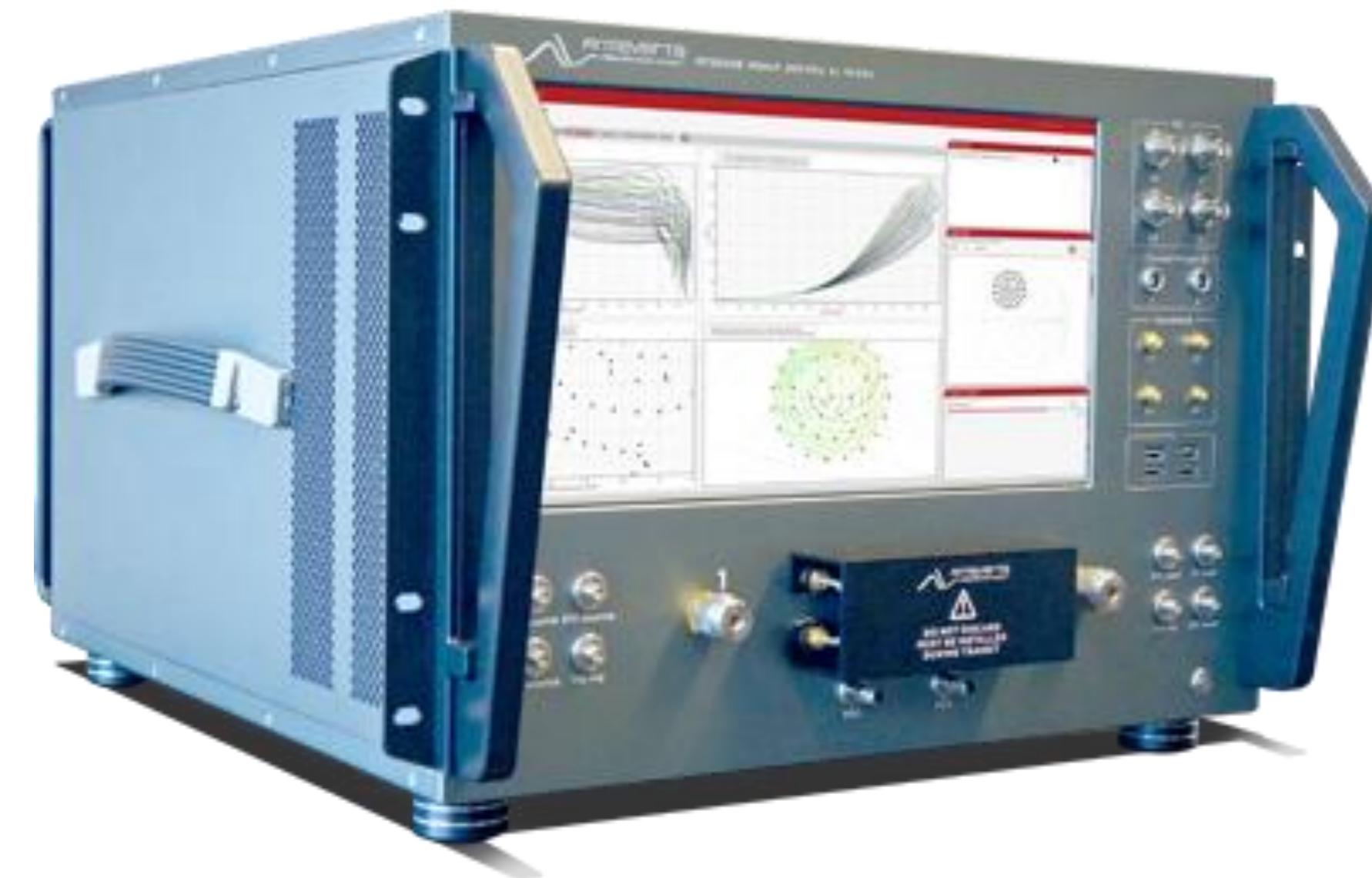
$x = \text{source } (s) \text{ or load } (l)$
 $n = \text{frequency band, e.g. baseband (0), fundamental (1) and harmonic (2 and up)}$
 $\Gamma_{\text{frequency}}(f_n)$ user defined reflection coefficient vs.



Step 3: Software iteration based on the reflection coefficient measurements at the DUT reference planes



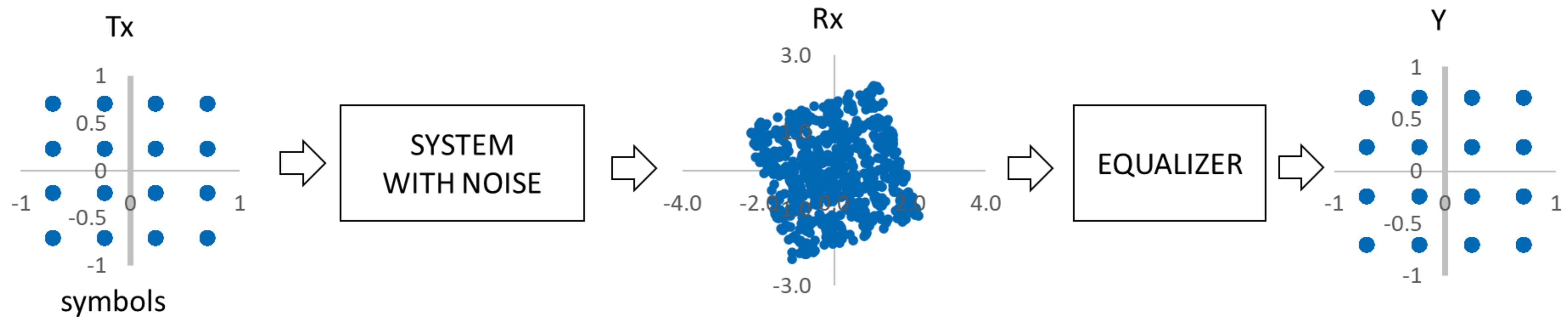
Key features



- Traditional analog and microwave techniques with low-frequency signal acquisition (A/D converters) and generation (Wideband AWG);
- Ultra fast CW and pulsed CW load pull
- Wideband ADCs allow measurement of wideband signals (power, ACPR, EVM)
- Frequency scalable: currently up to **67 GHz**
- System includes **6 VSGs** to generate custom modulations up to **1000 MHz** bandwidth
- Each VSG can be used as an active tuner
- VNA + NVNA + Oscilloscope + Signal Analyzer + Behavioral Model extraction in one solution



EVM measurements - background

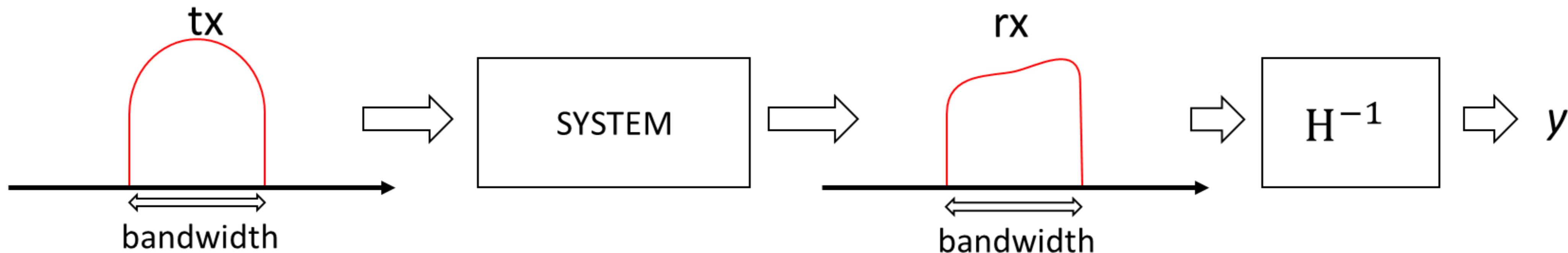


- linear and nonlinear distortion;
- thermal noise;
- ISI;

$$EVM = \sqrt{\frac{\sum |Y - T_x|^2}{\sum |T_x|^2}}$$

●●●● Generalized EVM measurement method

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$$Rx(f) = H(f)Tx(f) + D(f)$$

$$rx = h \otimes tx + d$$

d is the uncorrelated distortion

$$EVM = \sqrt{\frac{\sum |y - tx|^2}{\sum |tx|^2}} = \sqrt{\frac{\sum |h^{-1} \otimes rx - tx|^2}{\sum |tx|^2}}$$

Estimation of filter_{1,2} h

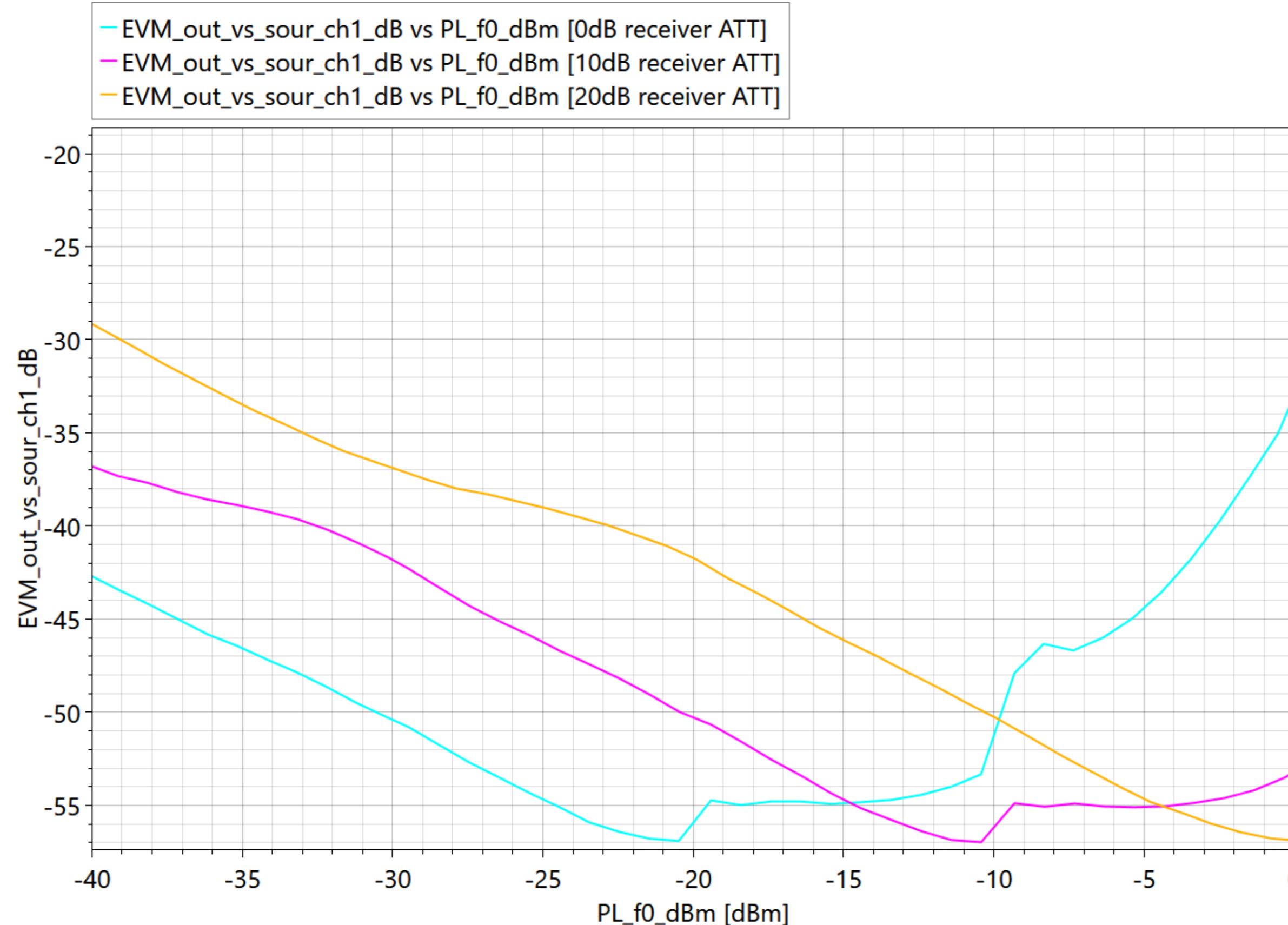
¹Linear Approximations of Nonlinear FIR Systems for Separable Input Processes, Martin Enqvist, Lennart Ljung, 2005

²Measurement Methods for Estimating the Error Vector Magnitude in OFDM Transceivers, Karl Freiberger, 2017



EVM measurements: noise floor

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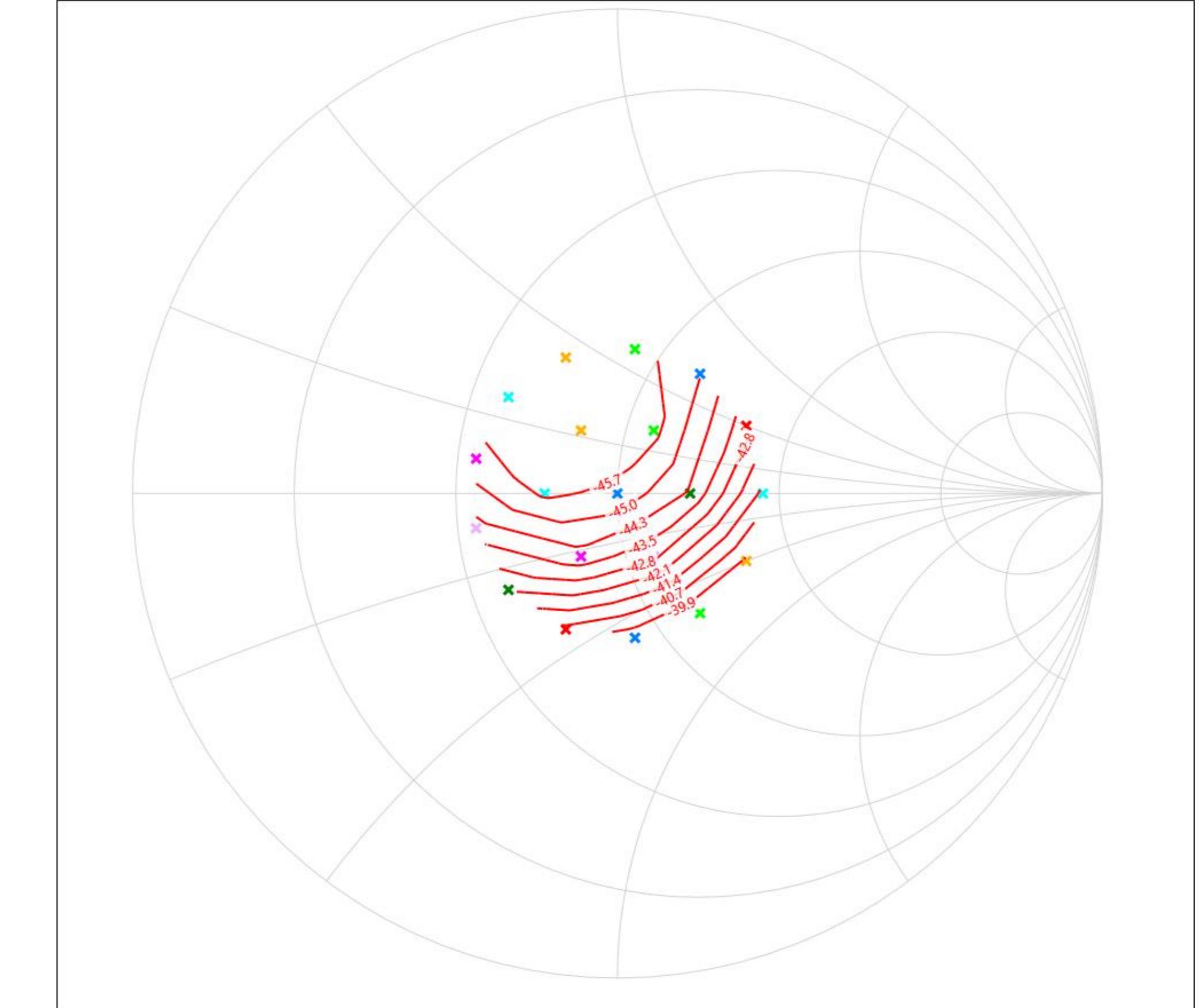
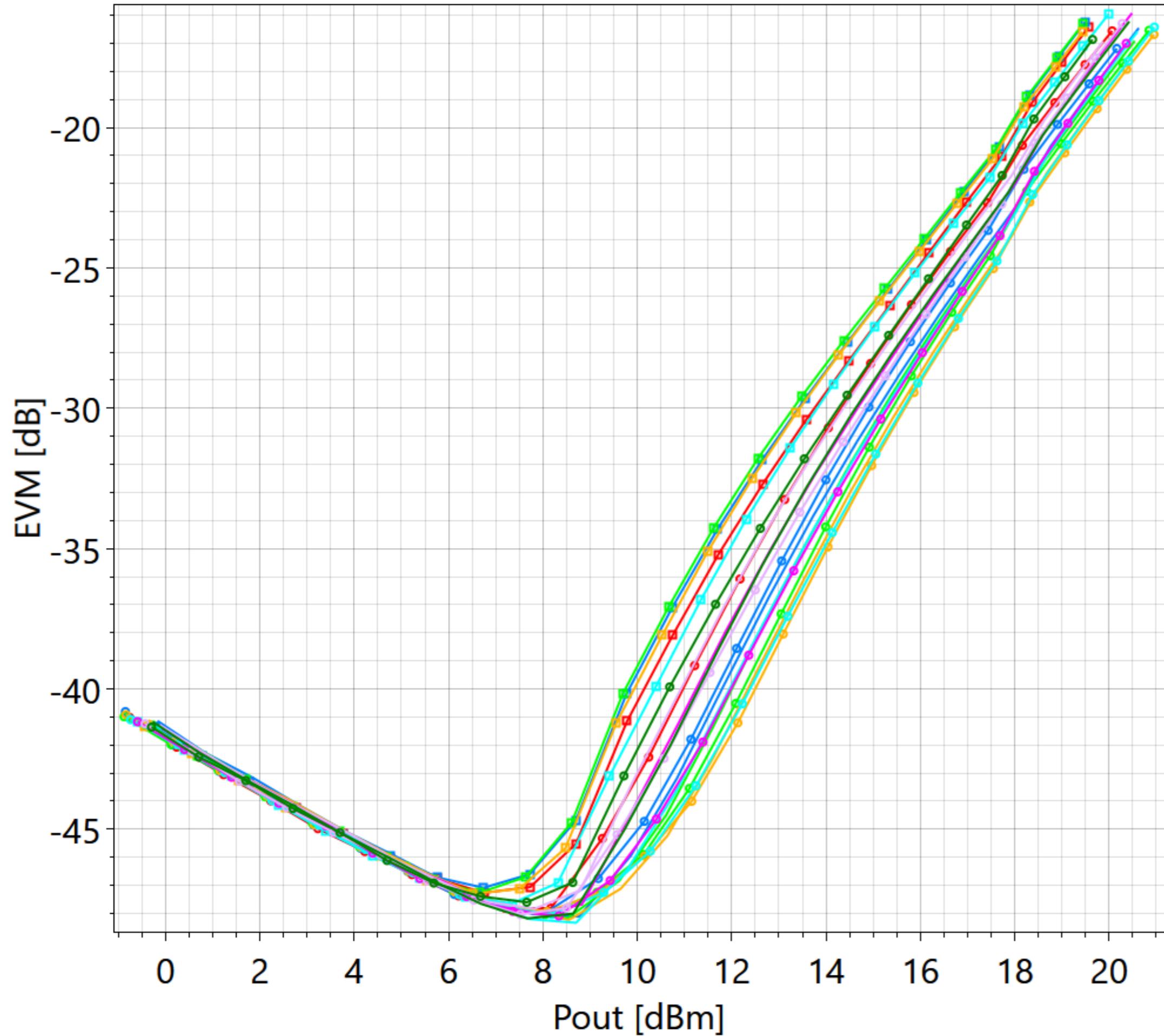
- Signal:
fr2_64qam_100M_120khz_cpofdm
- Carrier frequency = 9 GHz

Comments:

- Receiver stepping automated to optimize noise floor across power sweep

EVM measurements w/ active load pull

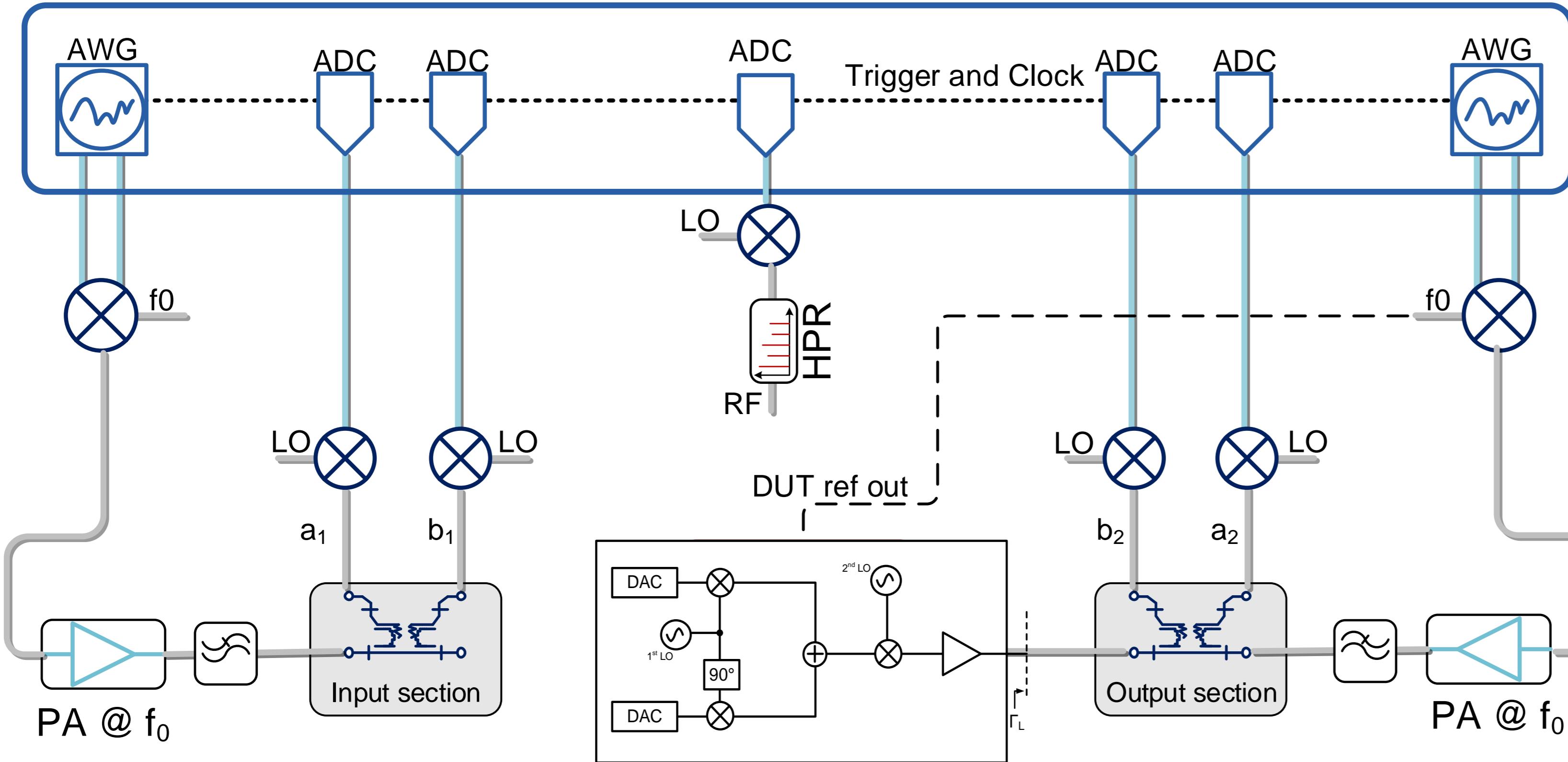
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- WLAN 802.11ax MCS9 3.5 GHz, BW = 320 MHz
- Measurements on a matched amplifier module



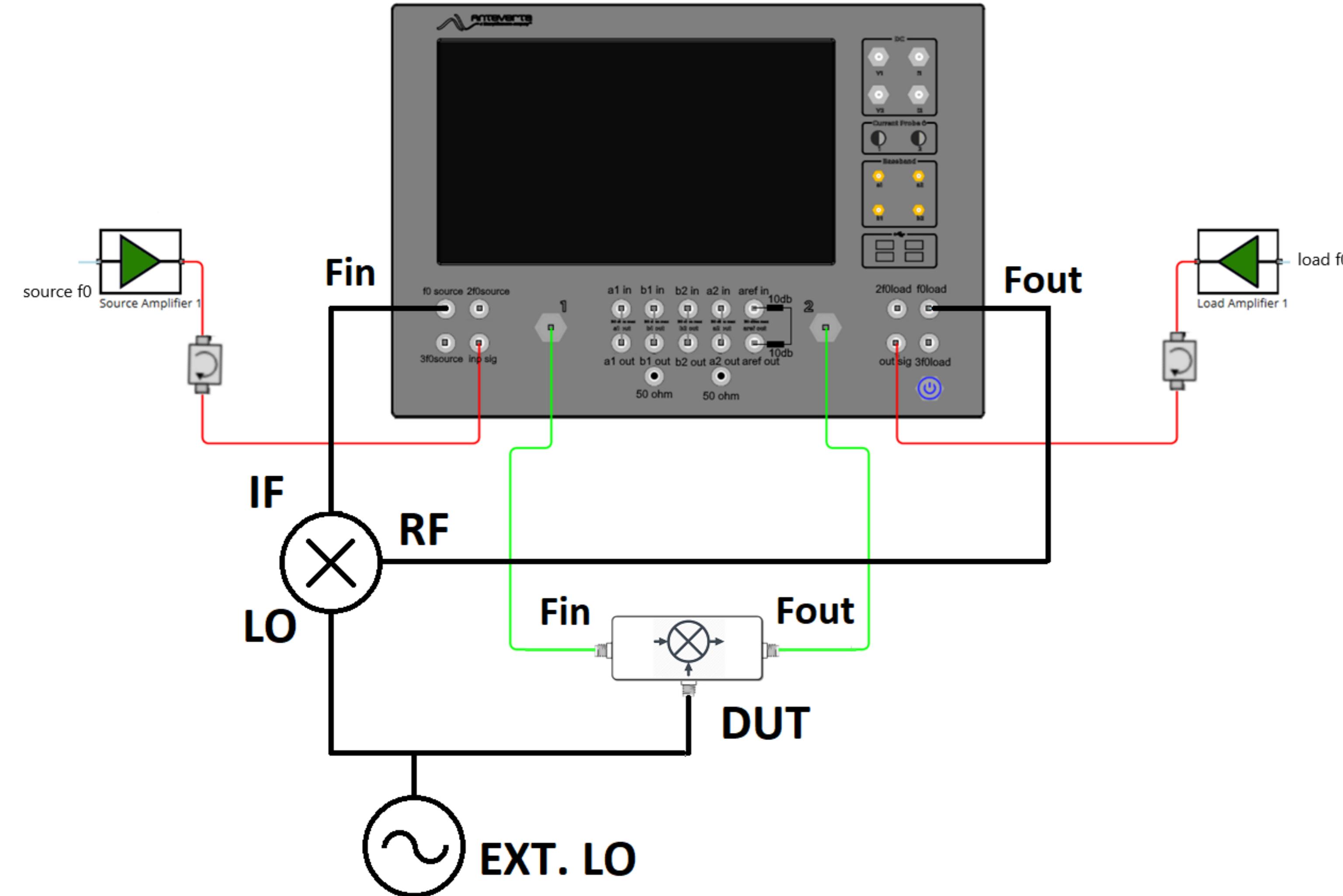
One-port load pull



- IQ modulator can be driven by an external LO (CW) signal at f_0 to achieve phase lock.
- CW, pulse CW and modulated testing are possible in this configuration



Load-pull on upconverters

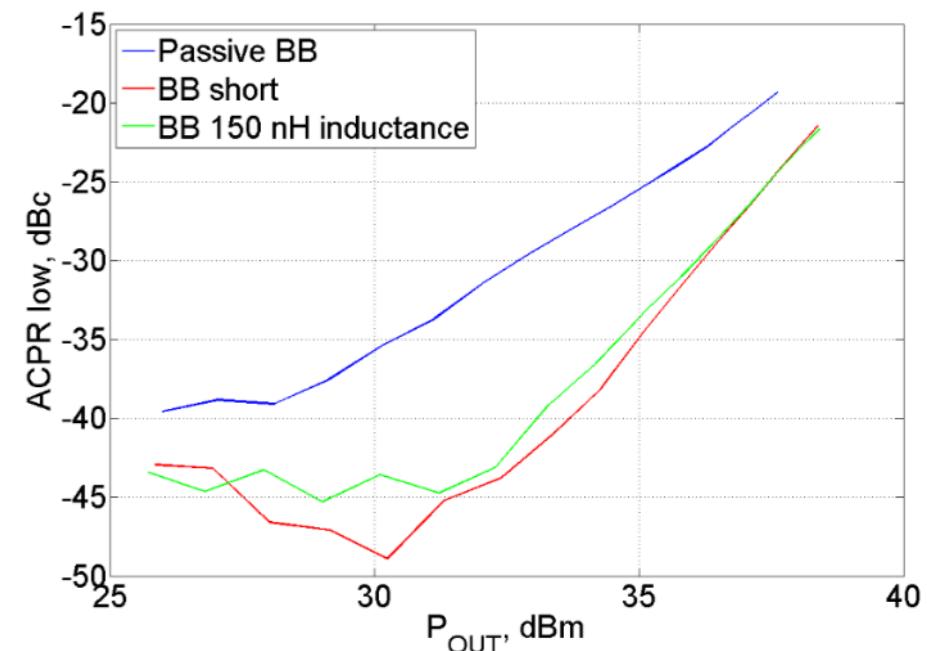
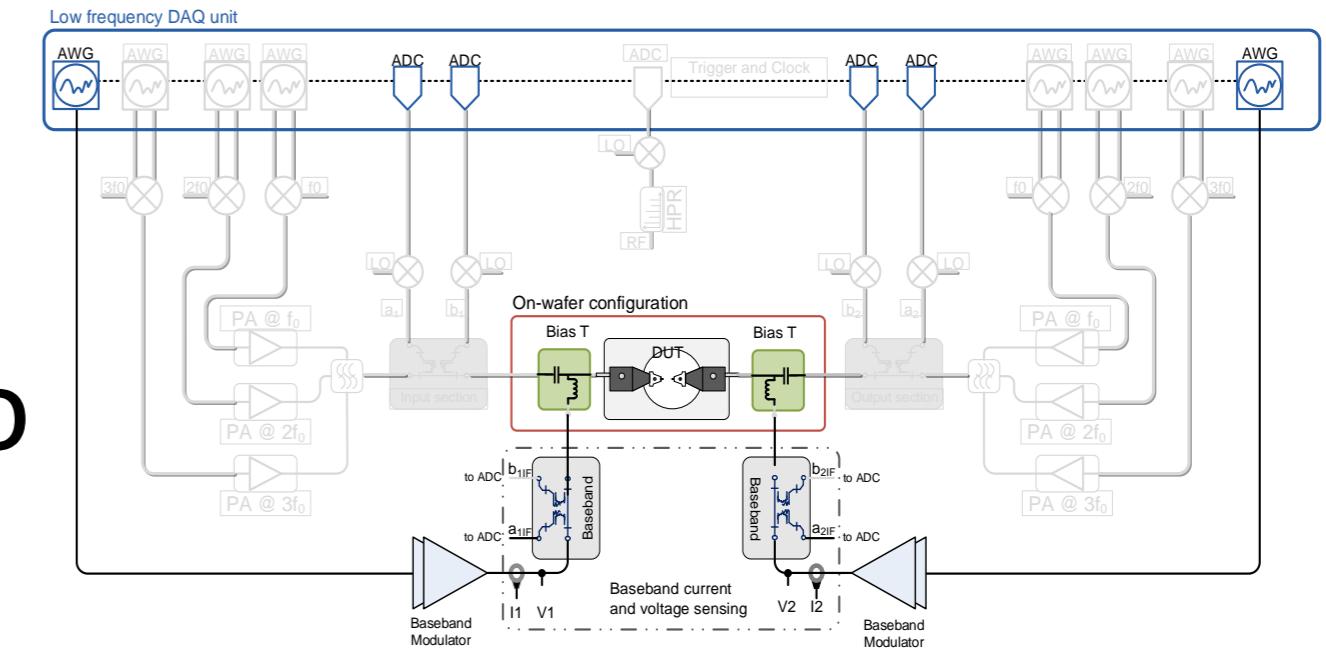


- An external LO is used by the DUT for the up-conversion from Fin to Fout
- The same LO is used with an auxiliary mixer to up-convert the system source signal (Fin) and generate the signal used for the load impedance control (Fout)

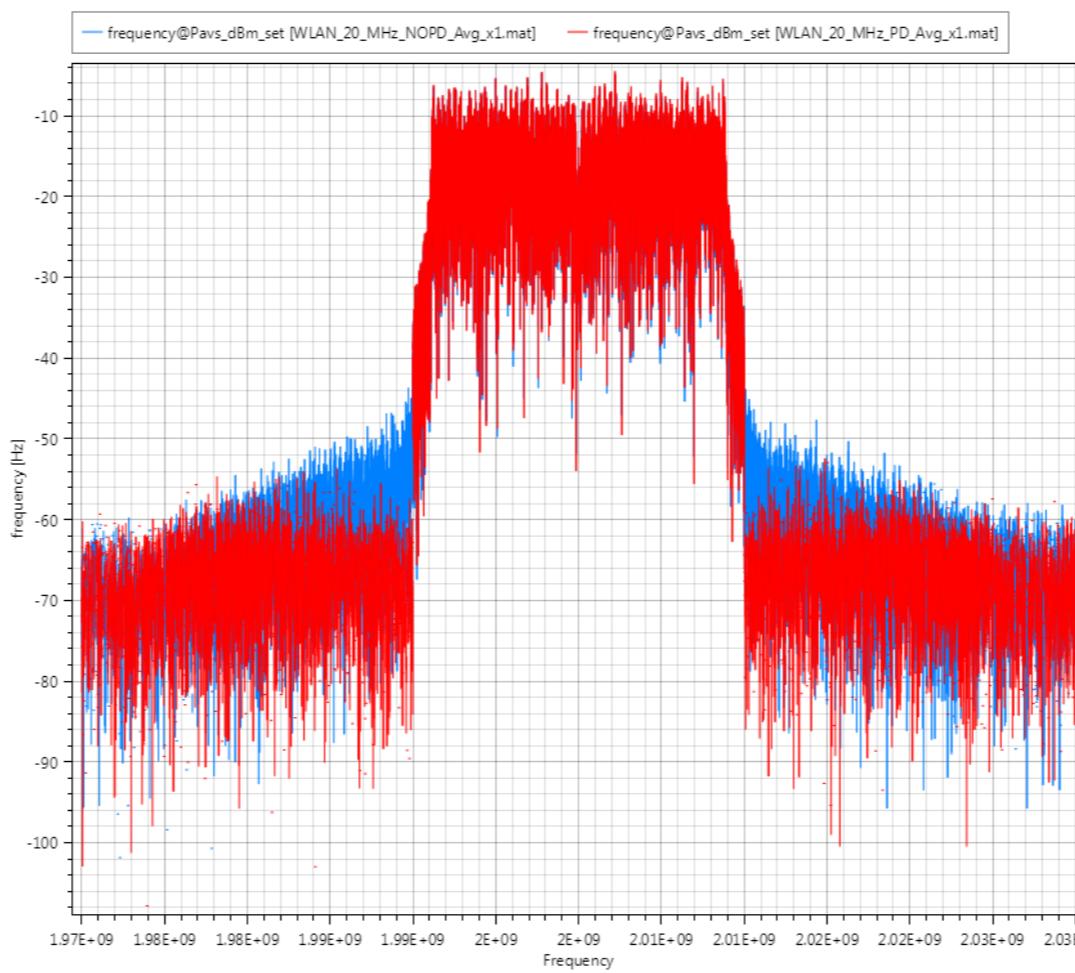


Additional requirements

- Baseband impedance control
 - Active load-pull applied to tune baseband impedance to enhance linearity (up to 200 MHz)
- DPD under load-pull conditions (spectral DPD, time-domain DPD)



...



mmW and sub-THz waveguide passive, active and hybrid-active vector-receiver load pull

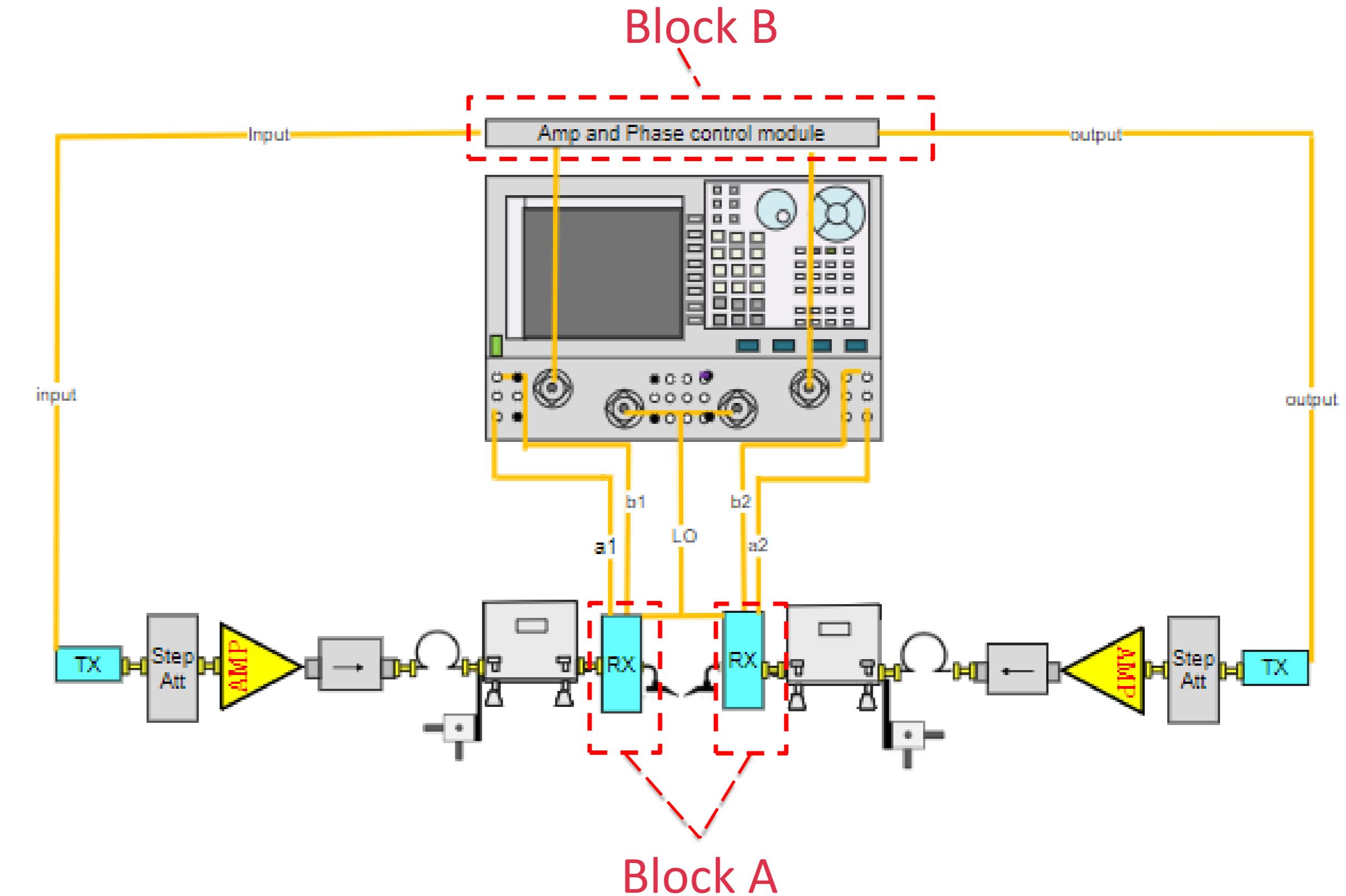




Waveguide load pull

Hardware to empower waveguide passive and hybrid-active load pull

- Low-loss couplers with integrated down-conversion (block A) allows for direct measurement of a- and b-waves
- Input and output amplitude and phase control module before up-conversion (block B) allows for high-resolution control of injected active tuning signal



••••• Waveguide passive and hybrid-active LP system

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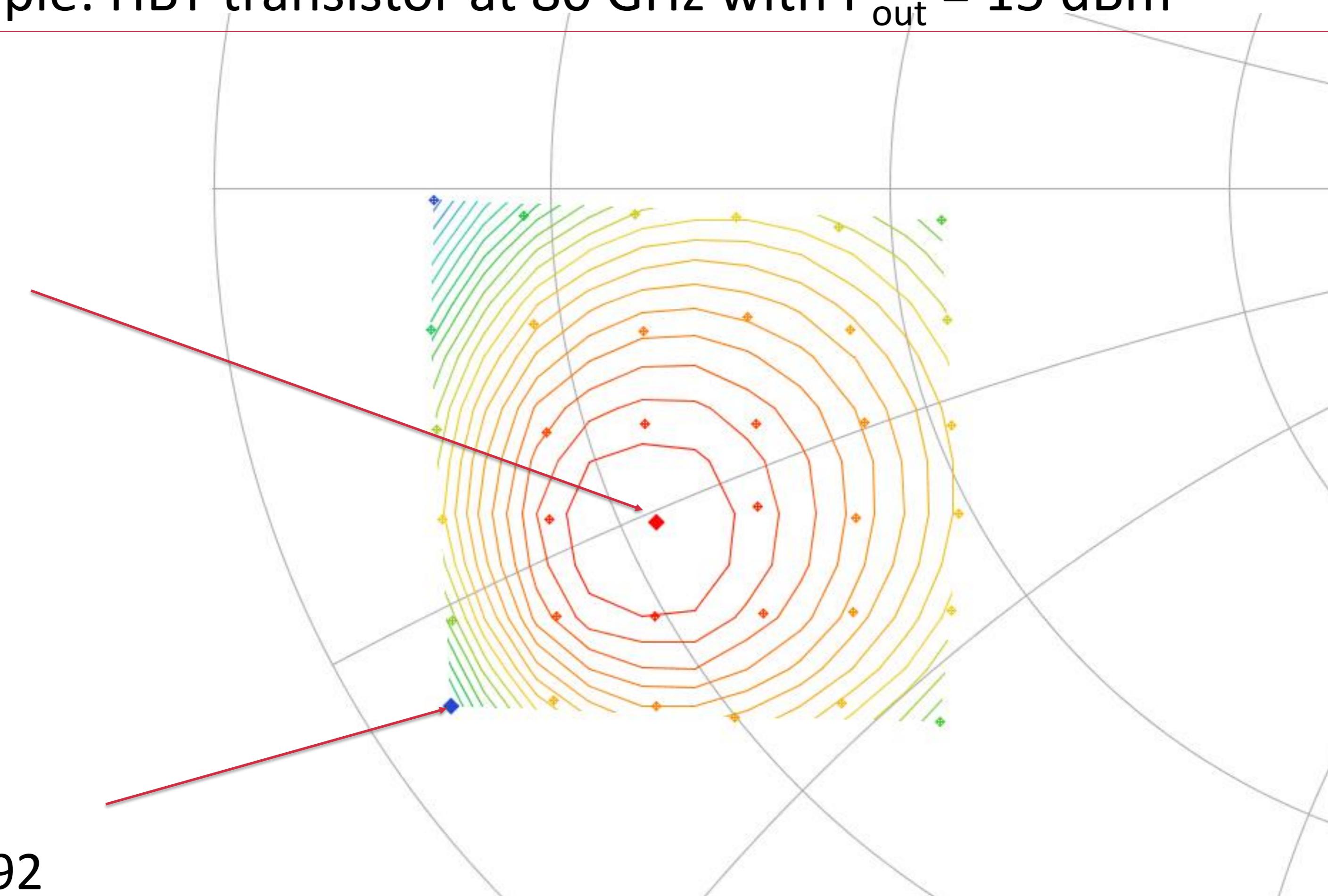
Waveguide passive and hybrid-active LP measurements

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Example: HBT transistor at 80 GHz with $P_{out} = 15 \text{ dBm}$

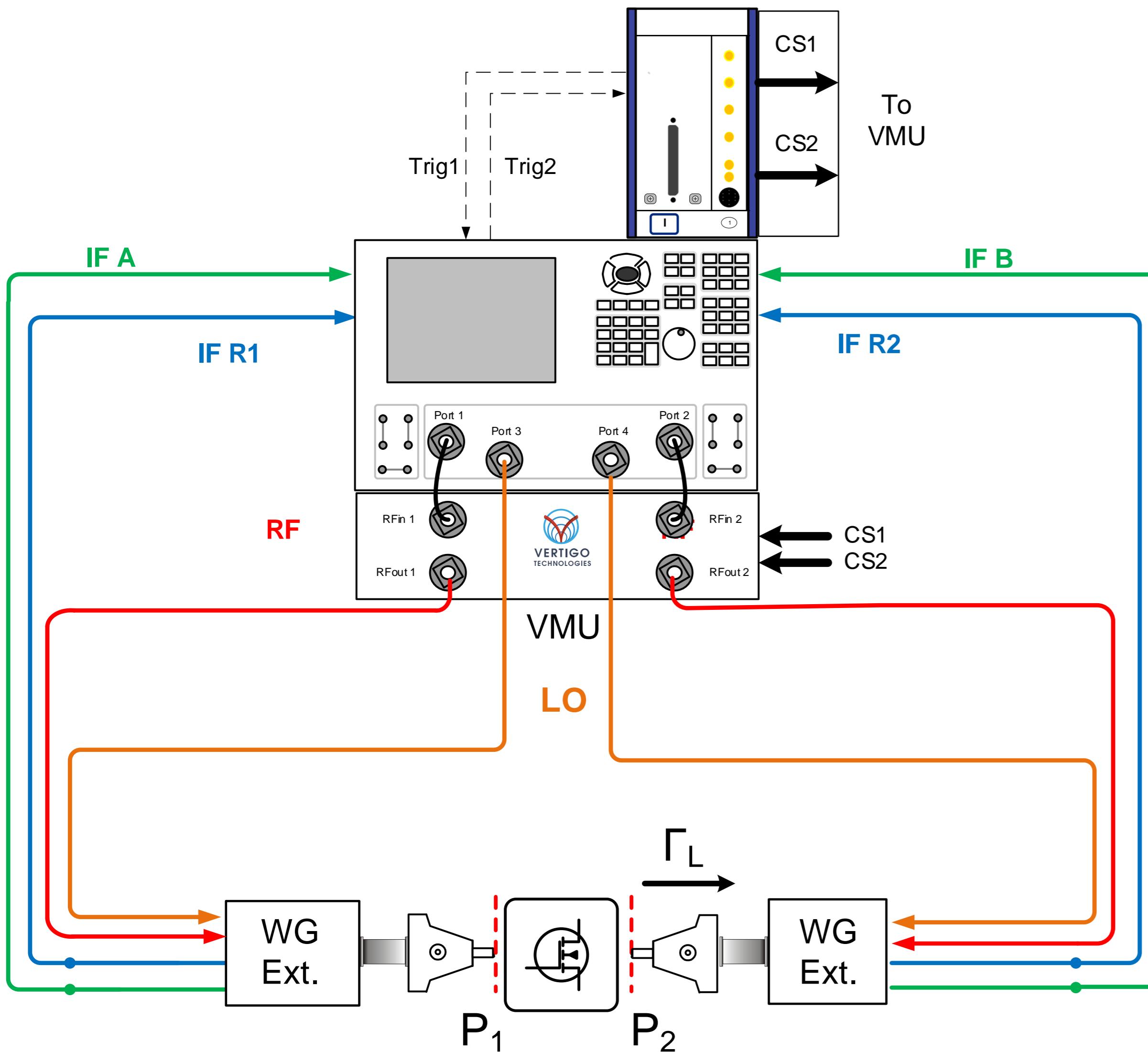
Optimum Eff
 $|\Gamma| \rightarrow 0.68$

Closed contours
 $|\Gamma| \rightarrow 0.92$



mmW and sub-THz active load pull

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What:

- Scalable active load-pull
- Based on VNA systems
- Up to 1 THz with WG-based extenders

How:

- Additional Vector Modulator Unit
- High accuracy DACs
- External control software

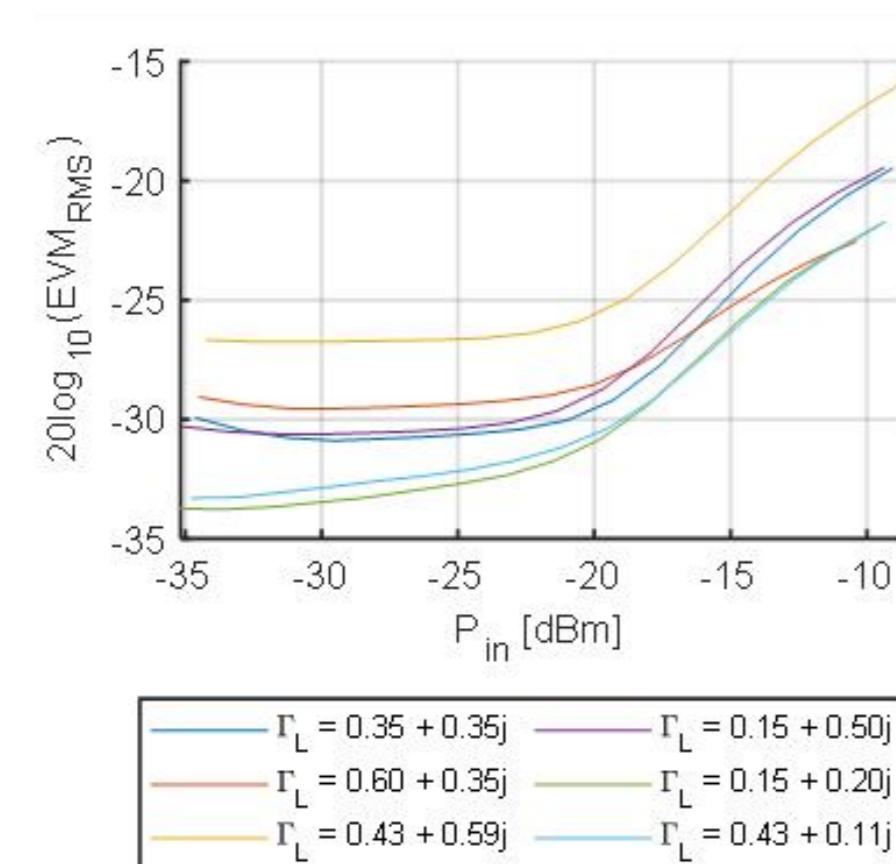
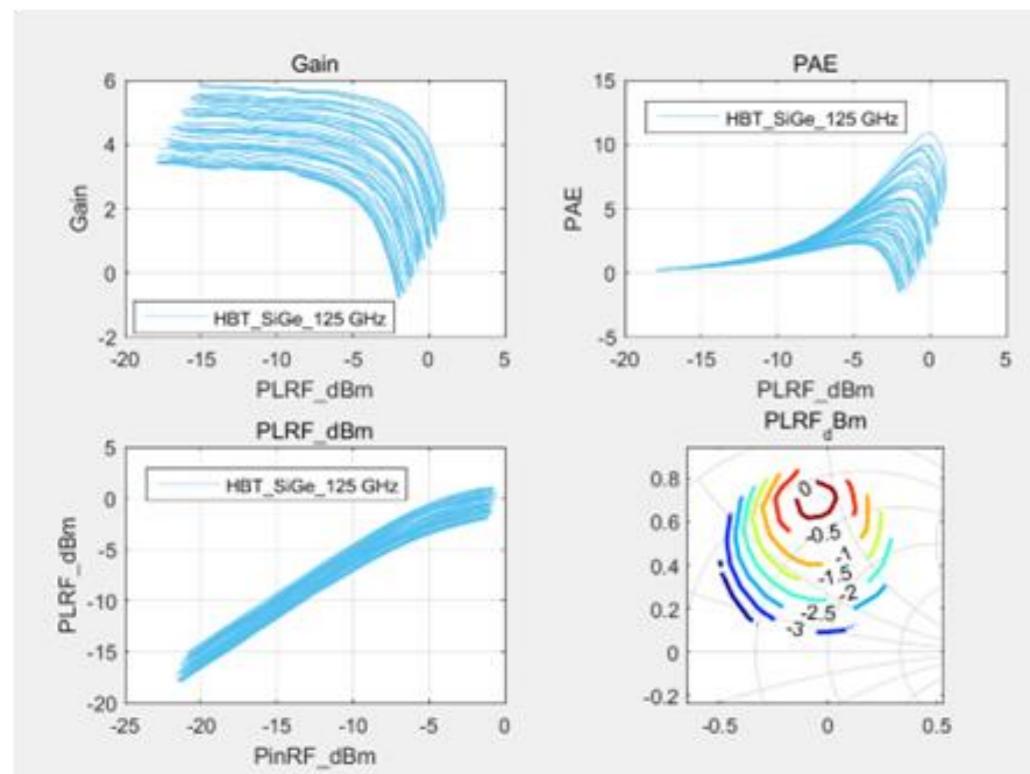
Why:

- Power controlled S-parameters
- Fundamental active load-pull

●●●● mmW and sub-THz active load pull system

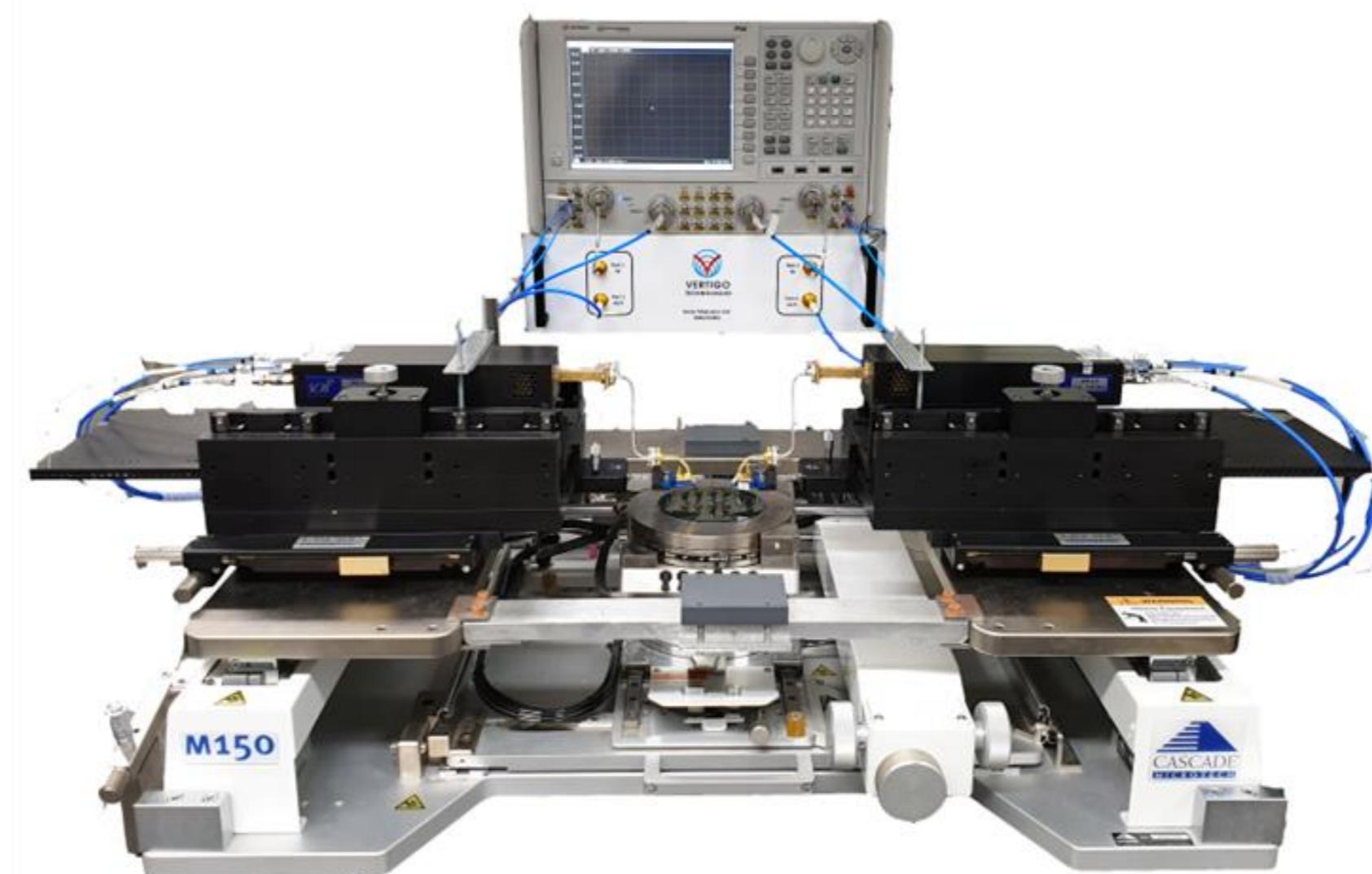
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Fundamental active Load-Pull



EVM estimation

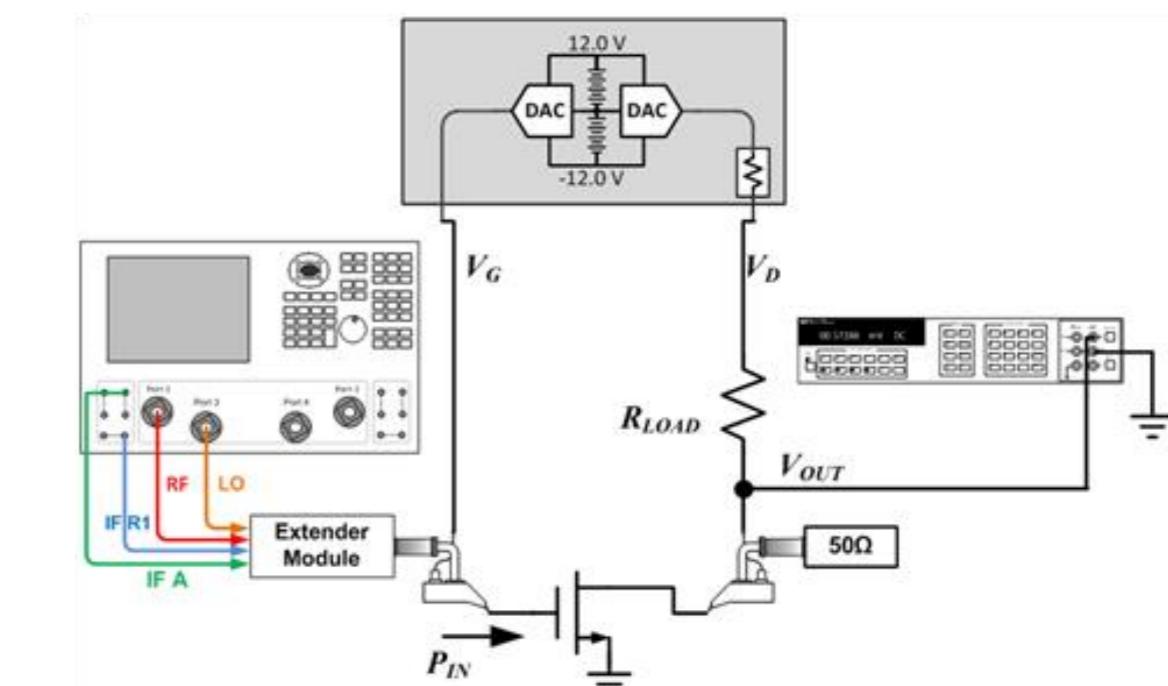
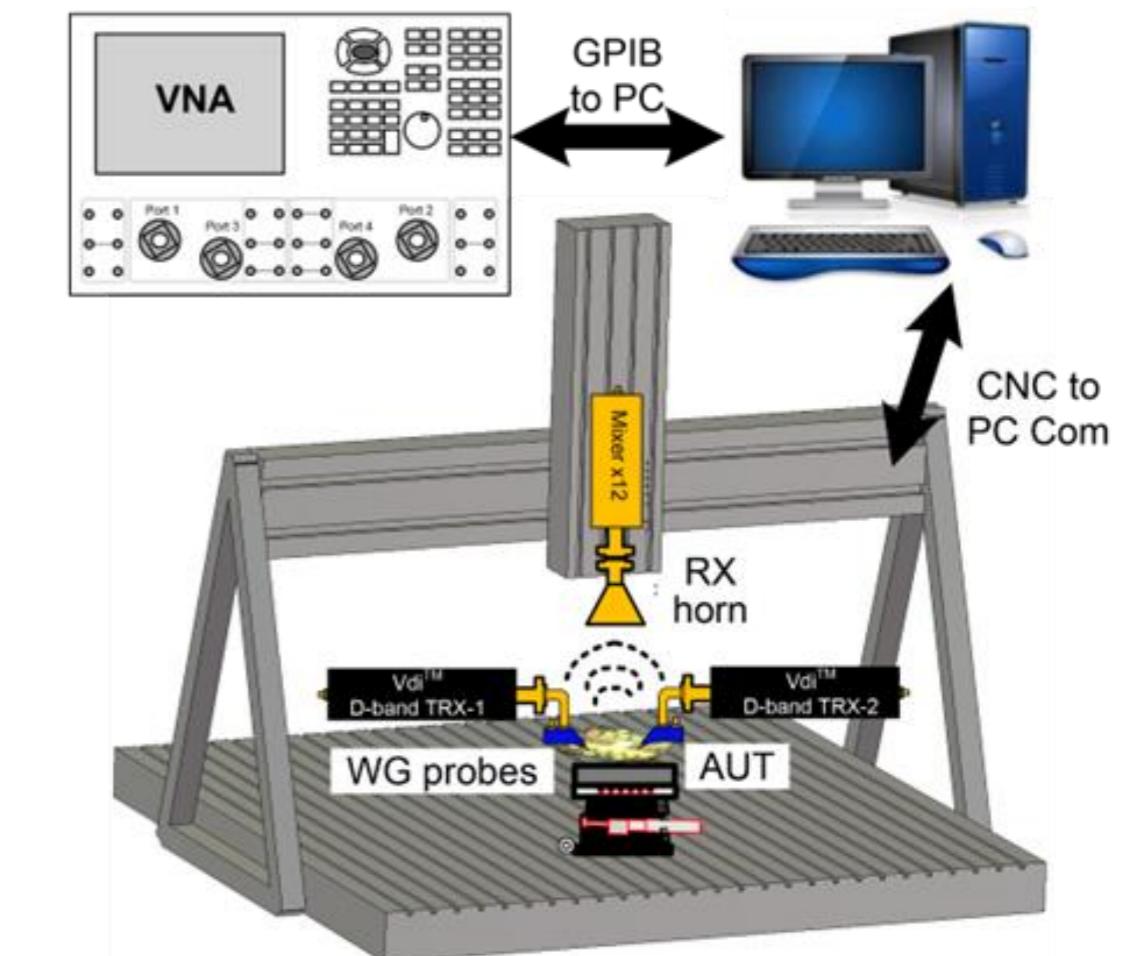
MMW-STUDIO MT920 Series



For all waveguide bandwidths up to 1THz
One unique software/hardware add-on
Many applications for 6G testing

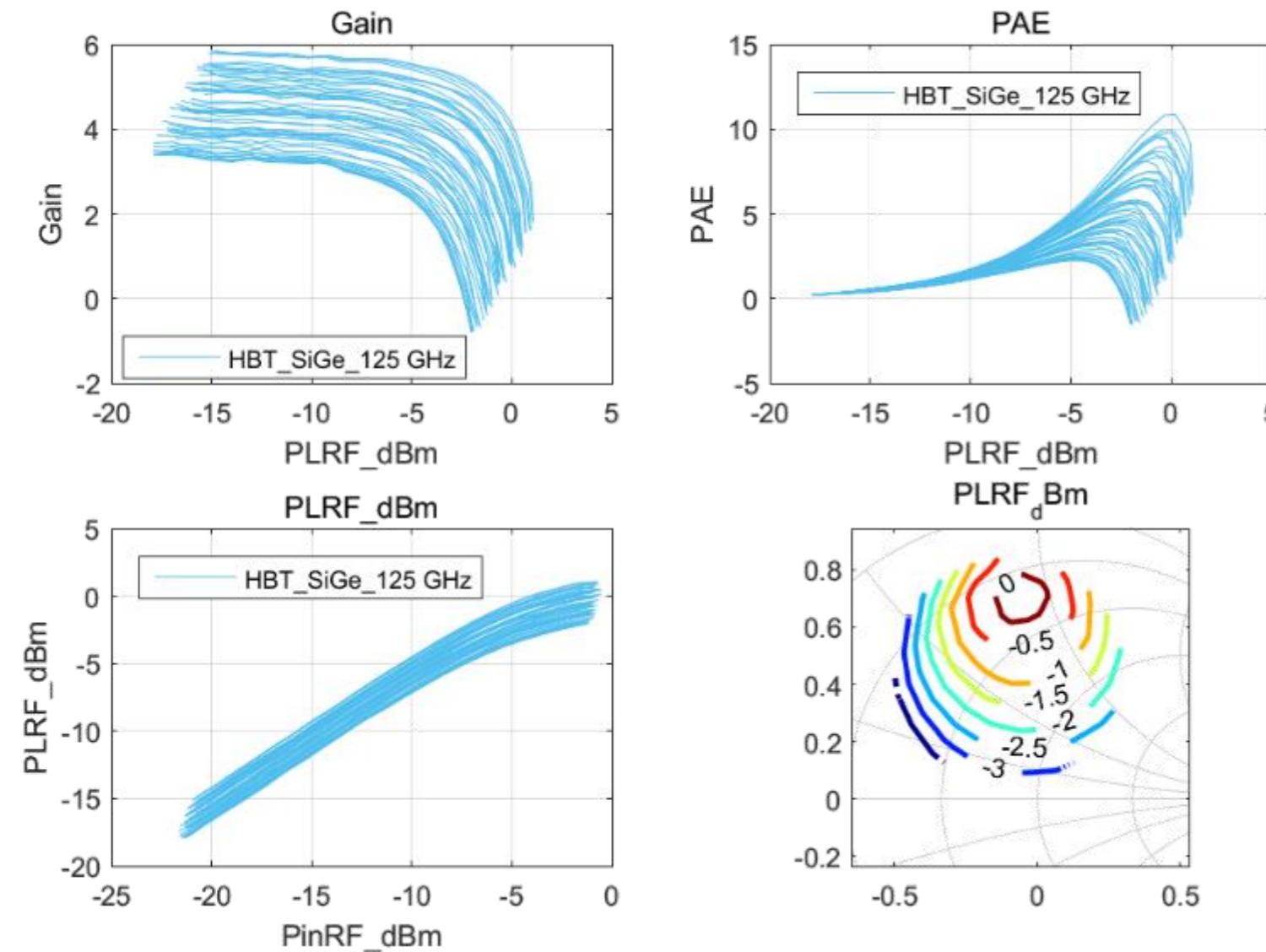


Over-the-air measurements

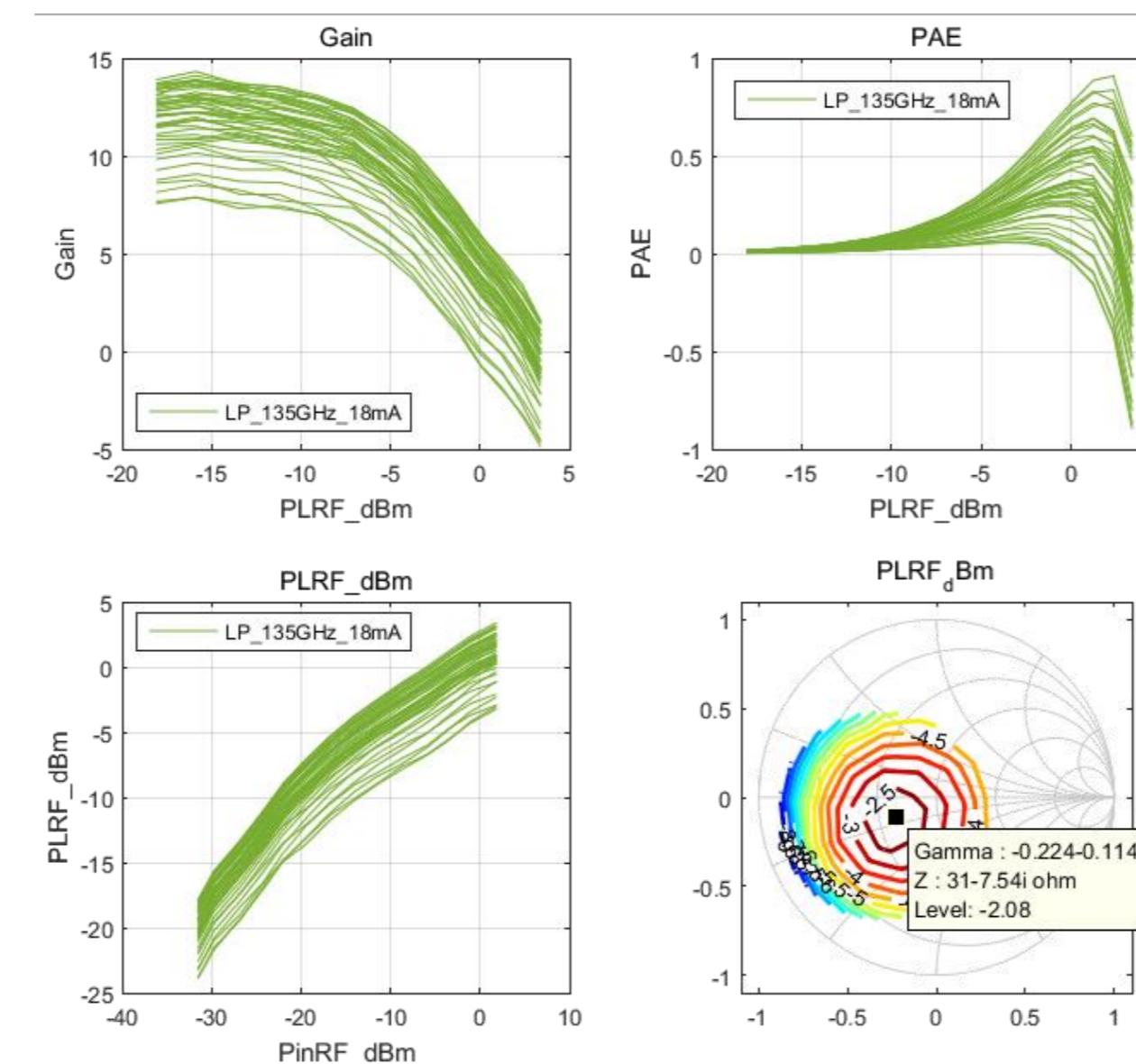


Responsivity measurements

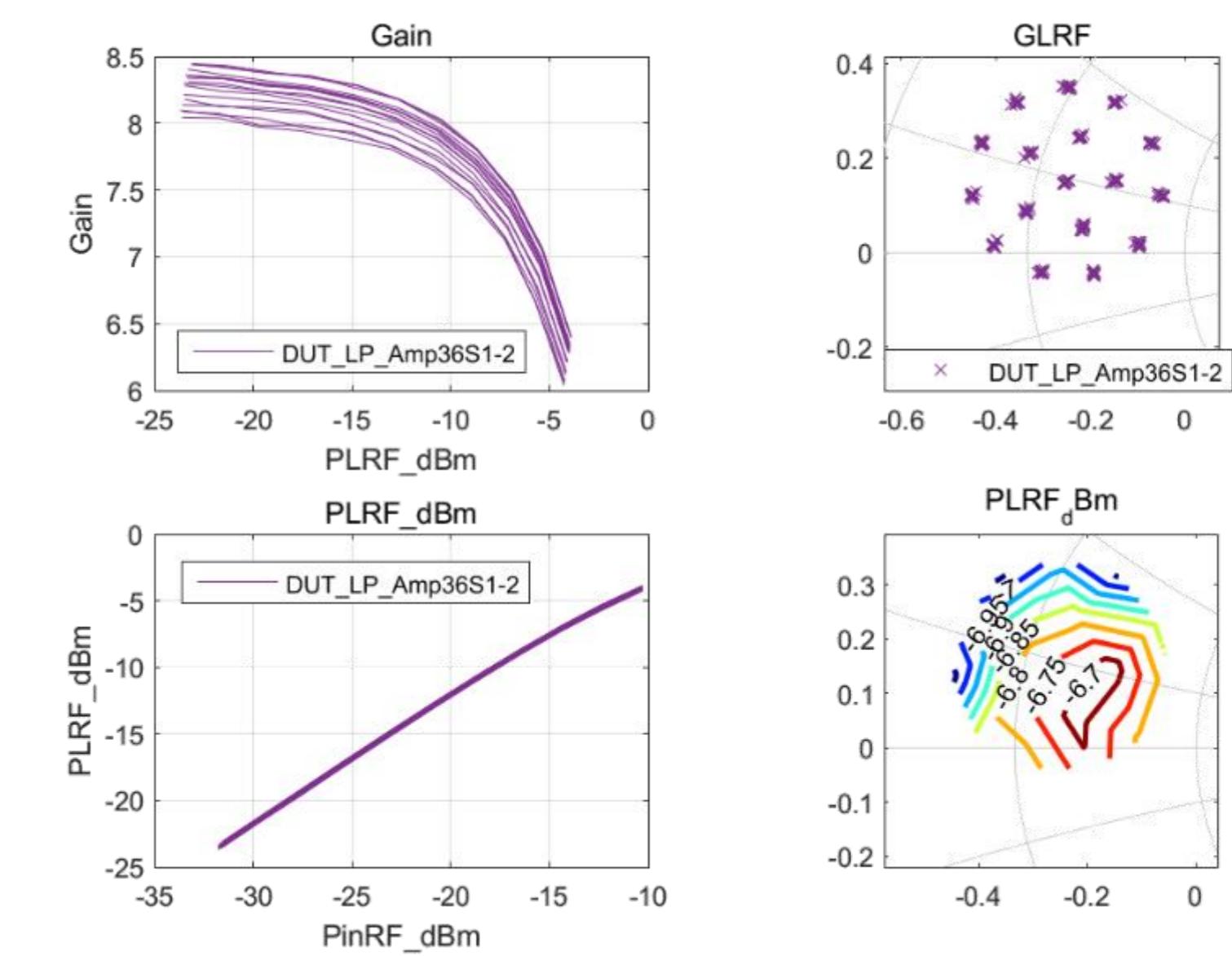
Characterization of small-cells: SiGe 130 nm double finger HBT at 125 GHz



Characterization of on-wafer multi-stage PA: SiGe BiCMOS at 135 GHz



Characterization of on-wafer multi-stage PA at 250 GHz



Thank You!

